

# Erzeugung und Anwendung ultrakurzer Laserpulse

## Generation and Application of Ultrashort Laser Pulses

Prof. Ursula Keller

*ETH Zurich, Switzerland*

*Festvortrag zur akademischen Feier aus Anlass der erstmaligen  
Verleihung des Young Researcher Award  
Erlangen Graduate School in Advanced Optical Technologies  
7. Januar 2008*

# Keller group: Thank you ...



## Ultrafast solid-state lasers: High average power (ML thin-disk laser)

Sergio Marchese, Cyrill Bär, Anna Enquist, Oliver Heckl, Dr. Thomas Südmeyer

## Ultrafast solid-state lasers: High pulse repetition rate

Max Stumpf, Andreas Oehler, Selina Pekarek, Dr. Thomas Südmeyer

## Ultrafast surface-emitting semiconductor lasers (ultrafast VECSELs and MIXSELs)

Deran Maas, Aude-Reine Bellancourt, Benjamin Rudin, Andreas Rutz, Martin Hoffmann, Dr. Yohan Barbarin, Dr. Thomas Südmeyer

## MBE and MOVPE growth in ETH clean room facility (FIRST-lab)

Dr. Matthias Golling

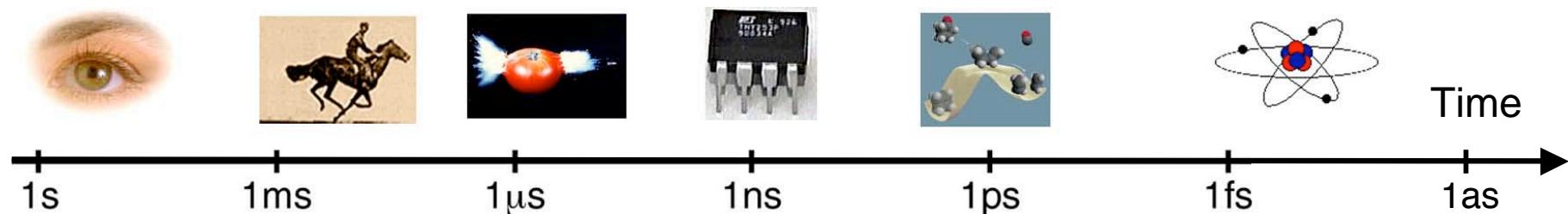
ETH FIRST Lab staff: Dr. Silke Schön (MBE), Dr. Emilio Gini (MOVPE)

## High field laser physics, attosecond pulse generation and science

Dr. Lukas Gallmann, Dr. Amelle Zair, Dr. Claudio Cirelli

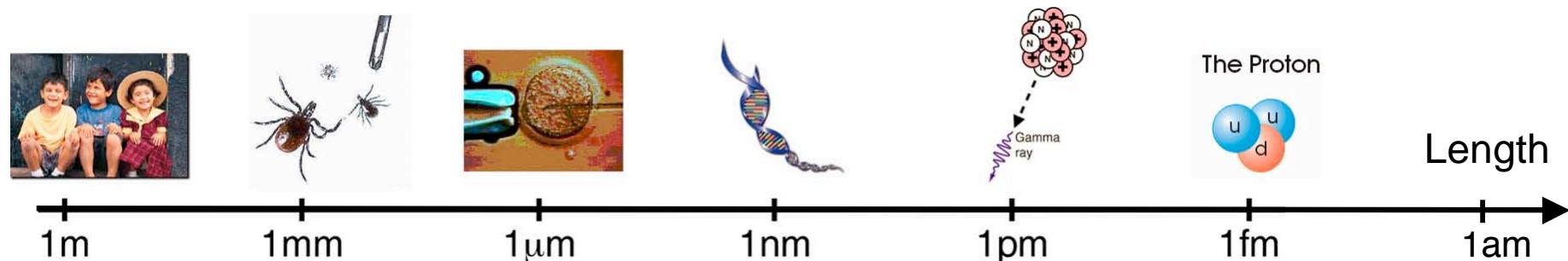
Christian Erny, Petrissa Eckle, Mirko Holler, Florian Schlapper, Matthias Weger

# Ultrafast laser physics (ULP)

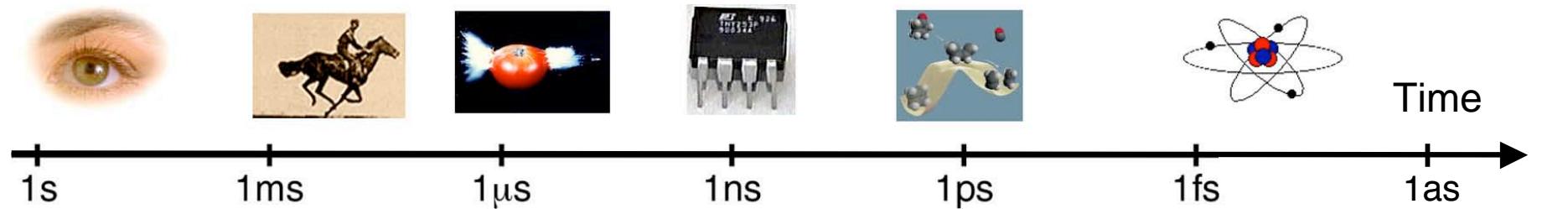


1 femtosecond = 1 fs =  $10^{-15}$  s

1 attosecond = 1 as =  $10^{-18}$  s



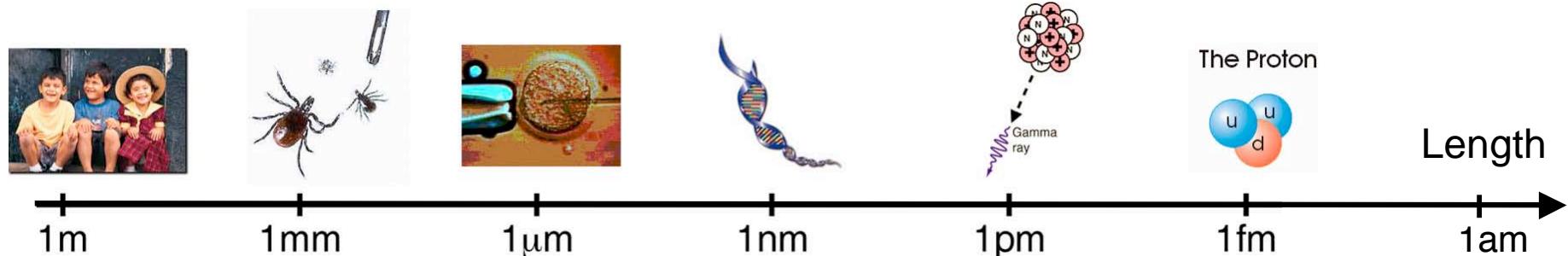
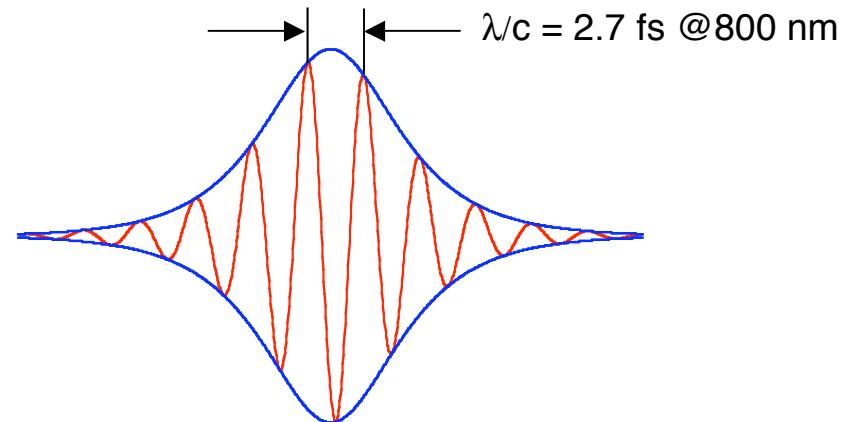
# Ultrafast laser physics (ULP)



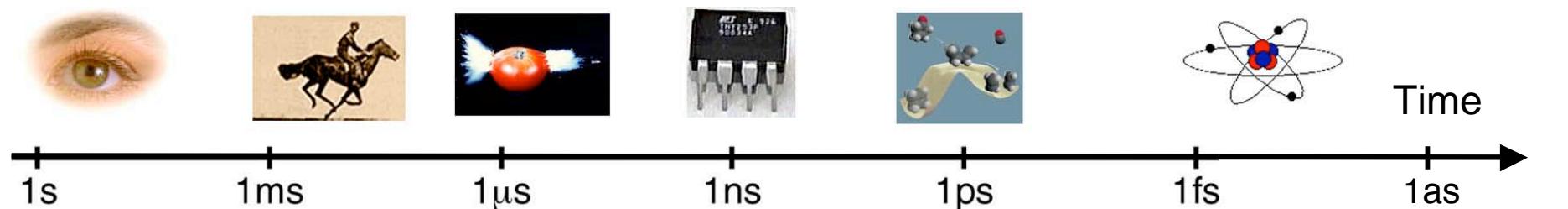
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Pulse generation directly from laser oscillators:  
milliseconds to femtosecond regime



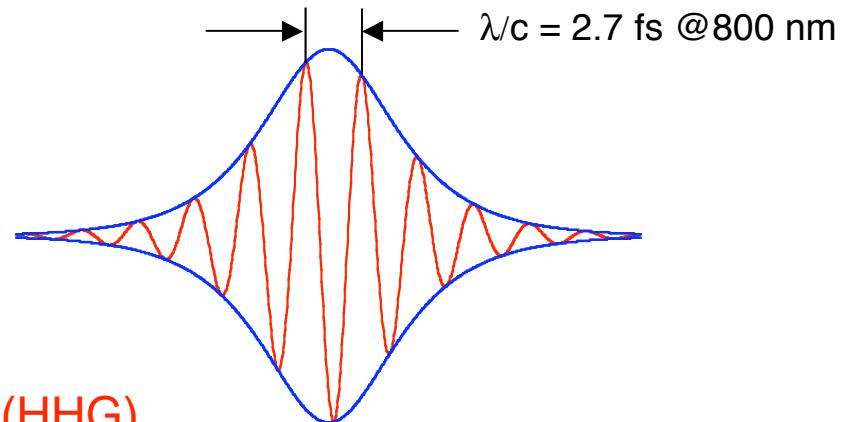
# Ultrafast laser physics (ULP)



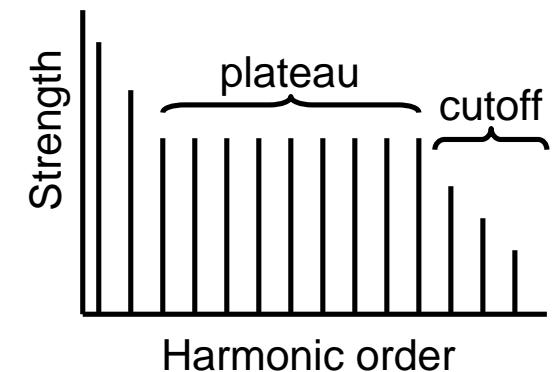
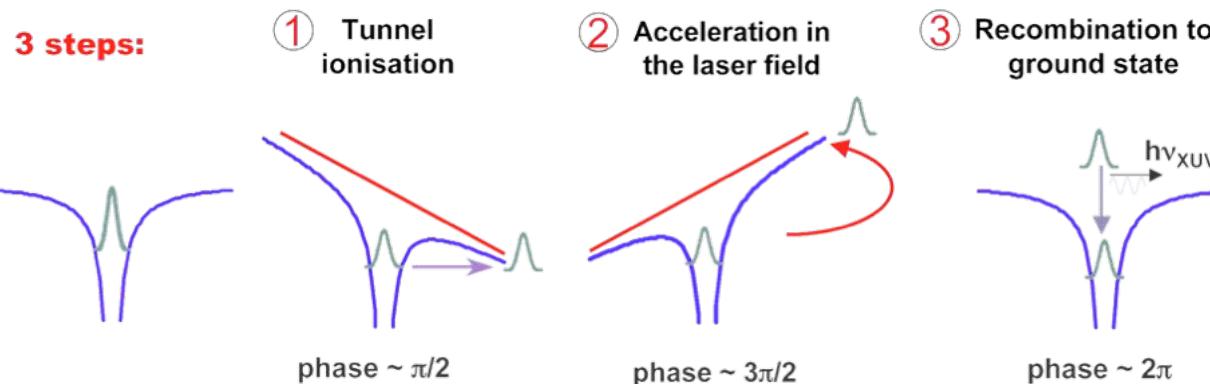
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Pulse generation directly from laser oscillators:  
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Attosecond regime: High Harmonic Generation (HHG)  
VUV to soft-X-ray regime



- **Good time resolution (short pulses)**  
measurements of fast processes
- **High pulse repetition rates**  
optical communication  
clocking and interconnects
- **High peak intensity at moderate energies**  
nonlinear optics  
precise material processing  
high field physics
- **Broad optical spectrum**  
frequency metrology (frequency comb)  
optical coherence tomography (OCT)

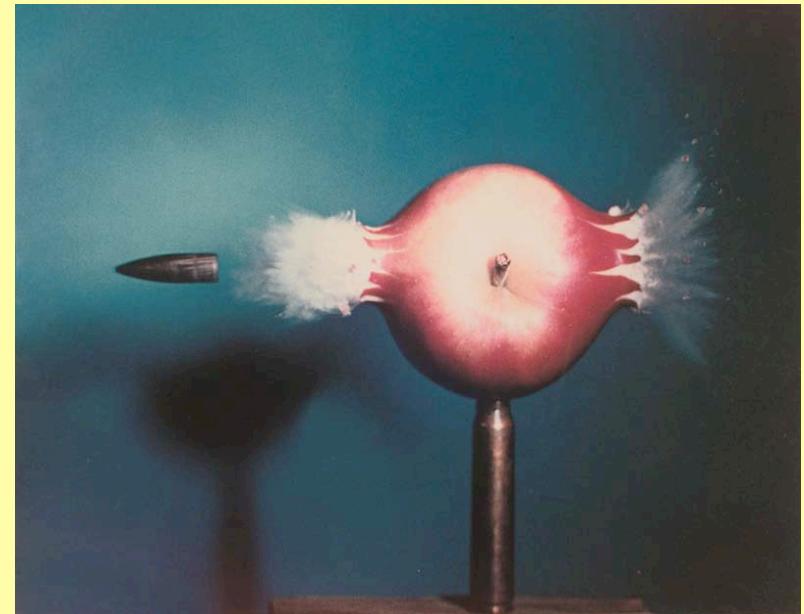
# Applications of ultrafast lasers

- **Good time resolution (short pulses)**  
measurements of fast processes

Time resolution limited by pulse duration

similar to flash photography:

- **High pulse repetition rates**  
optical communication  
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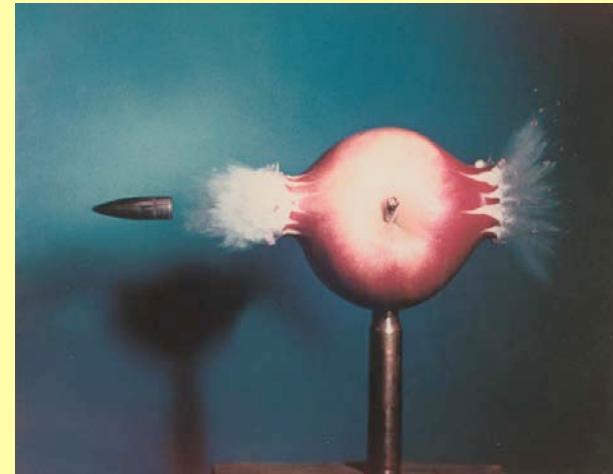


Triggered flash lamps for  $\approx 1 \mu\text{s}$  exposure time  
1964 by Harold E. Edgerton, MIT

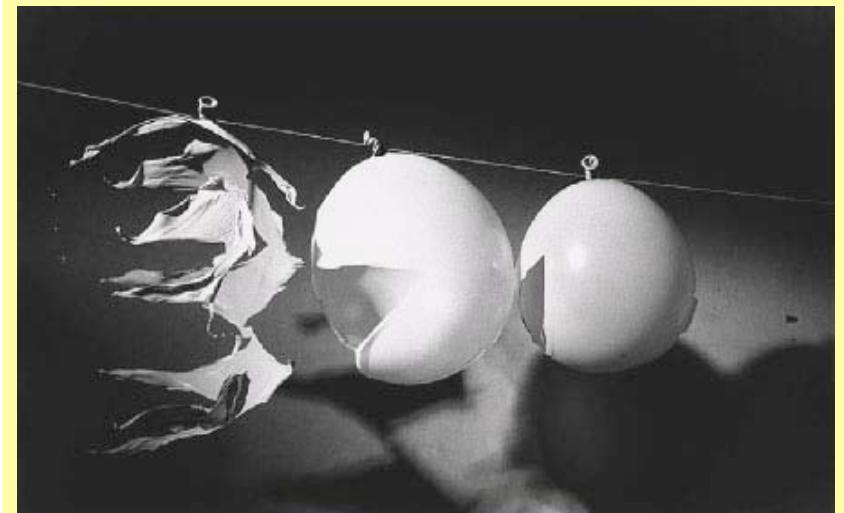
# Applications of ultrafast lasers

- **Good time resolution (short pulses)**  
measurements of fast processes

Time resolution limited by pulse duration (e.g. flash photography)  
Harold E. Edgerton, MIT



- **High pulse repetition rates**  
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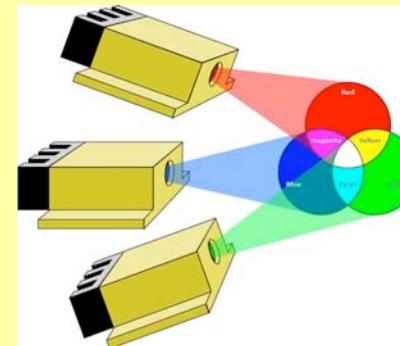
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- **Good time resolution (short pulses)**  
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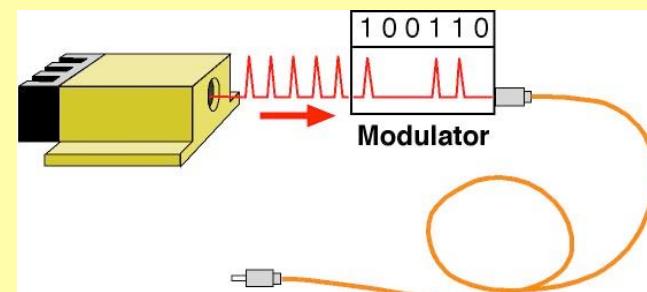
- **High pulse repetition rates**  
optical communication  
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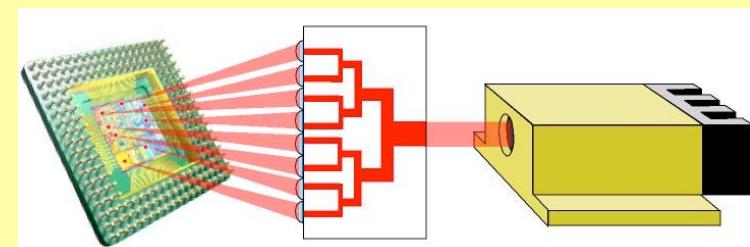
Laser display (RGB source):



Optical communication:



Optical clocking and interconnects:



# Applications of ultrafast lasers

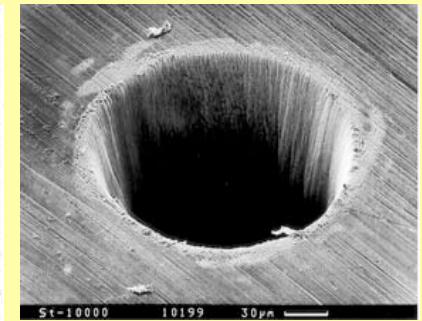
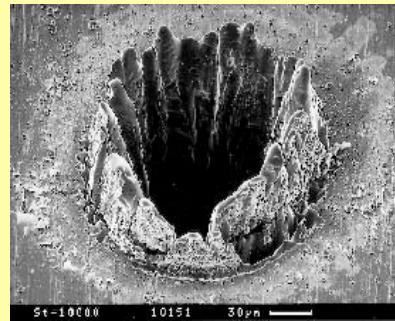
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- **High pulse repetition rates**  
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clocking and interconnects

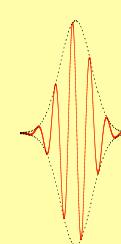
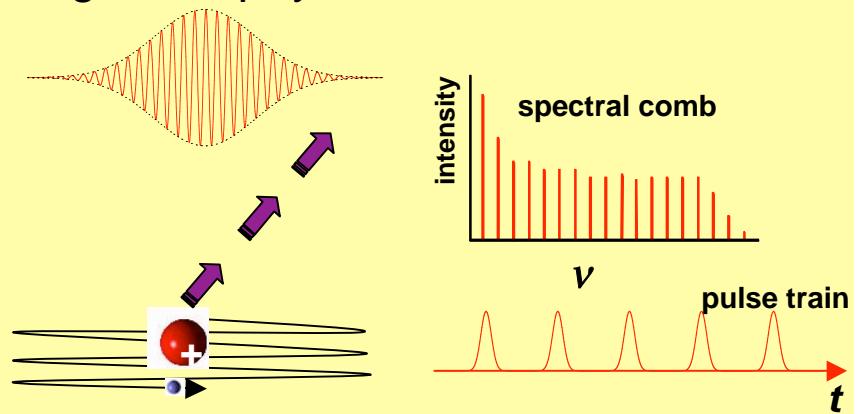
- **High peak intensity at moderate energies**  
nonlinear optics  
precise material processing  
high field physics

- **Broad optical spectrum**  
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optical coherence tomography (OCT)

Precise material processing:



High field physics: attosecond science

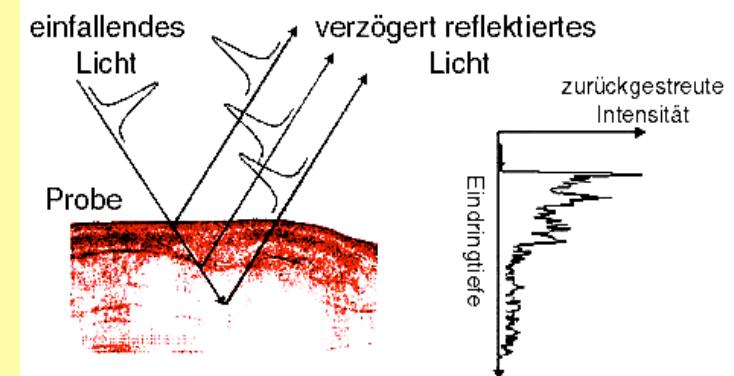


just 1 (or few) recollision(s)

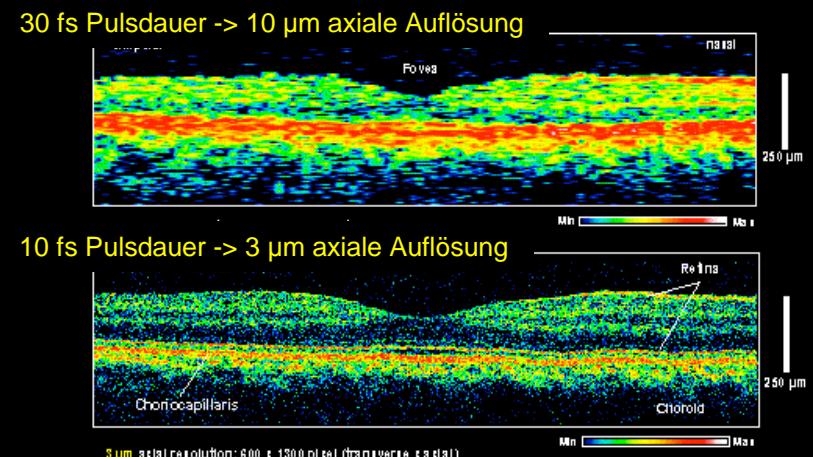
# Applications of ultrafast lasers

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OCT:



## Normal versus Ultrahigh Resolution OCT



Prof. J. G. Fujimoto, MIT

OCT image of retina (around fovea)  
Early detection of retinal detachment

# Applications of ultrafast lasers

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Optical clock (>100 THz):

- time is defined by a certain number of oscillations within a given time interval:  
„the higher the frequency the more accurately the time interval is defined“

- **0.001 Hz:** Sand clock

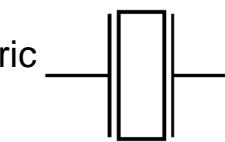


- **1 Hz:** Mechanical clock



- **10 MHz:** Quartz oscillator

Piezoelectric  
crystal  
resonator



- **9 GHz:** Atomic clock

GPS



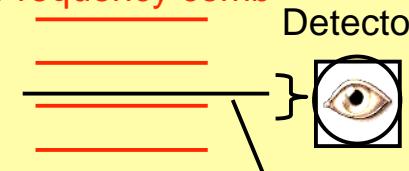
# Applications of ultrafast lasers

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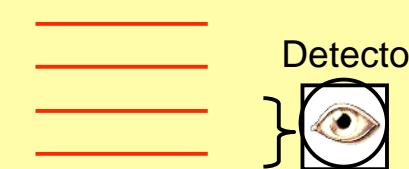
Optical clock (>100 THz):

- time is defined by a certain number of oscillations per fixed time interval:  
„higher frequency more accurate clock“
- optical frequency: too high for counting
- frequency comb of ultrafast laser:  
detector measures the difference in frequency  
= beating signal
- beating signal measures the „distance“ of unknown frequency to the lines in the frequency comb
- optical frequency becomes measurable
- Potential measurements:  
„are fundamental constants constant?“

## Frequency comb

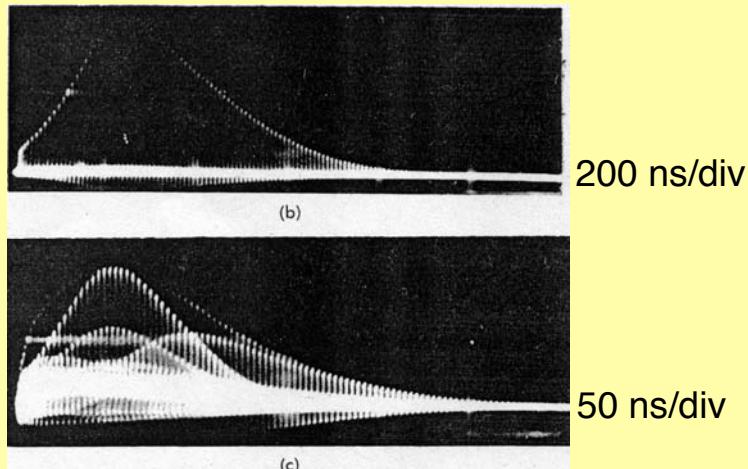


Unknown frequency

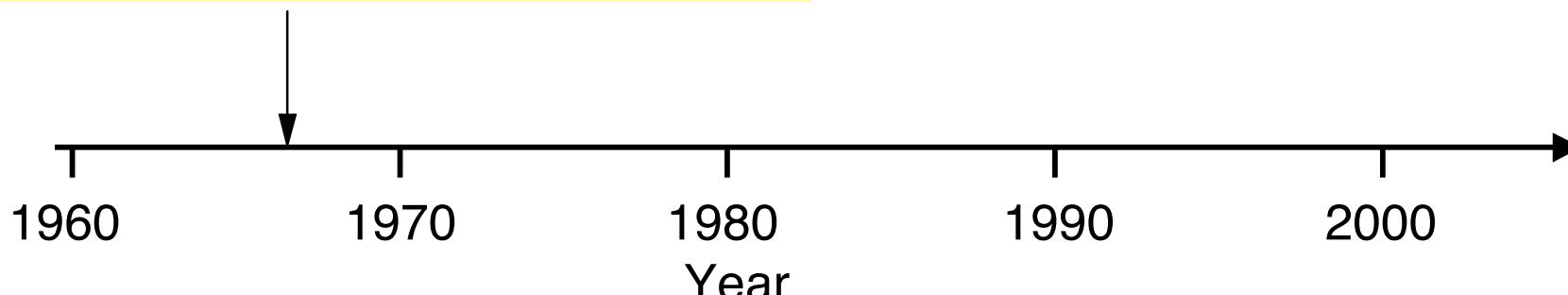


# Ultrashort pulse generation with modelocking

A. J. De Maria, D. A. Stetzer, H. Heynau  
*Appl. Phys. Lett.* **8**, 174, 1966



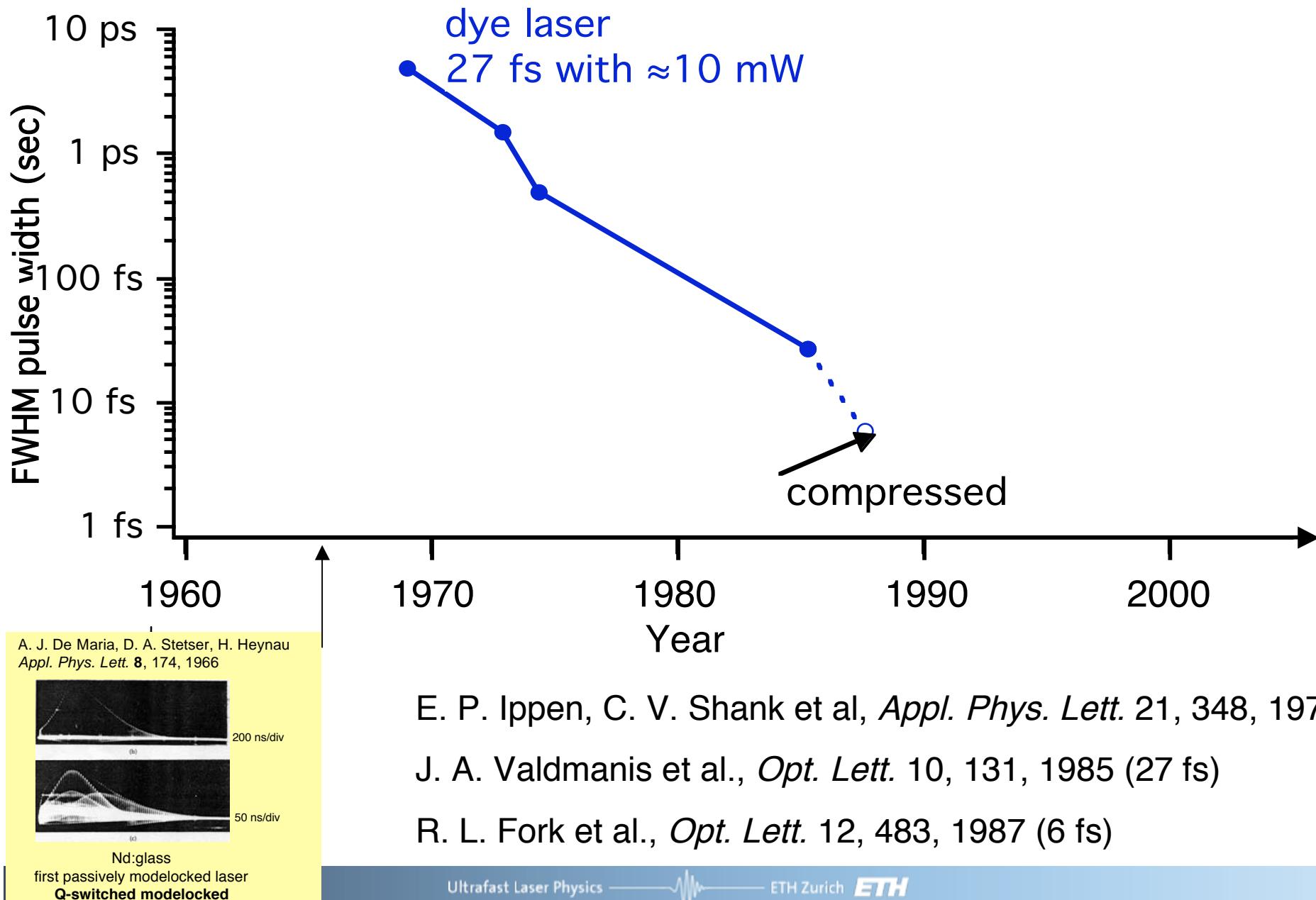
Nd:glass  
first passively modelocked laser  
**Q-switched modelocked**



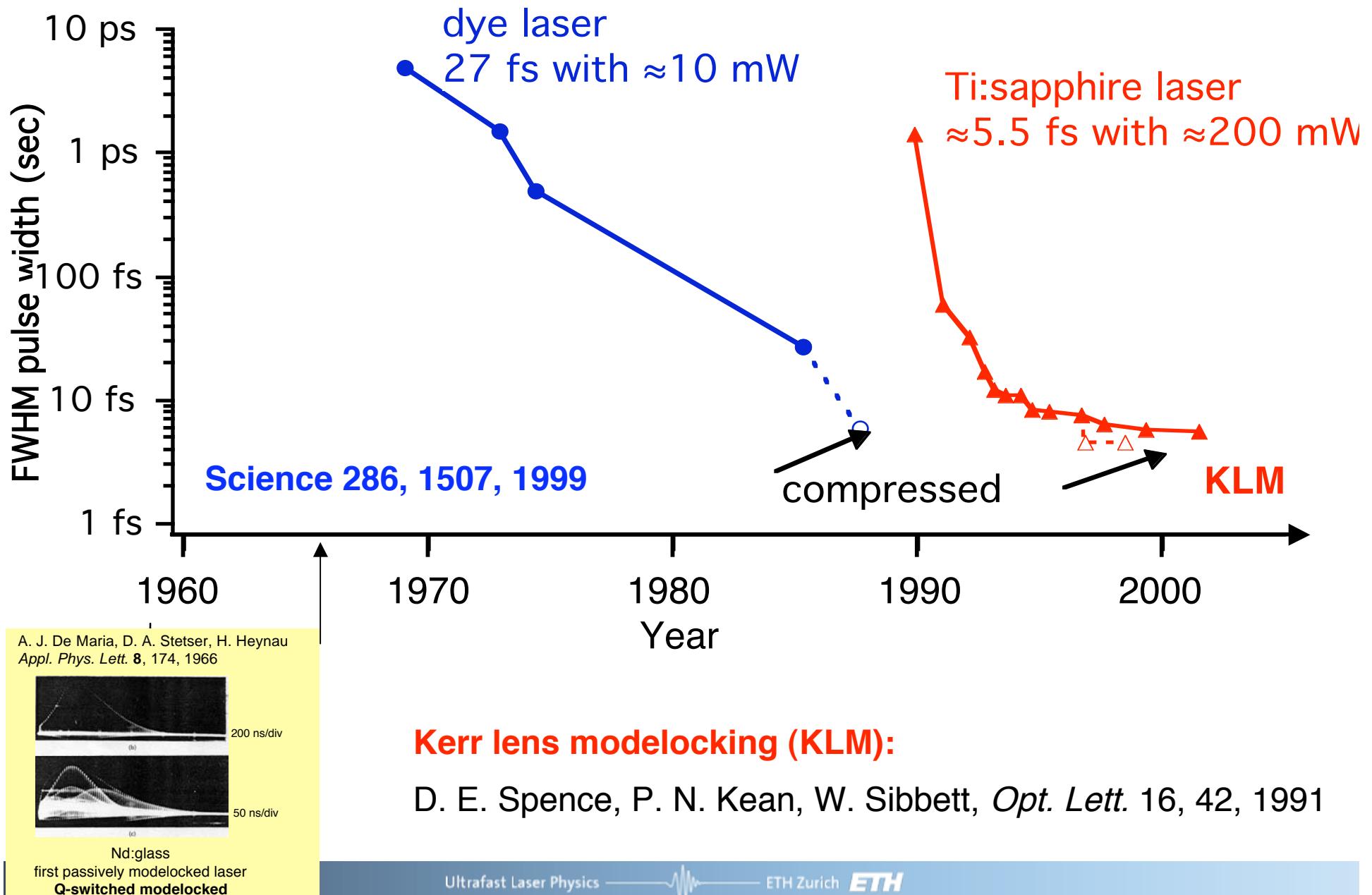
**Flashlamp-pumped  
solid-state lasers**

**Diode-pumped solid-state lasers**  
(first demonstration 1963)

# Ultrashort pulse generation with modelocking



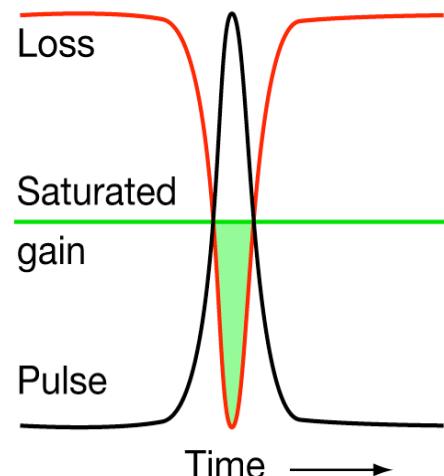
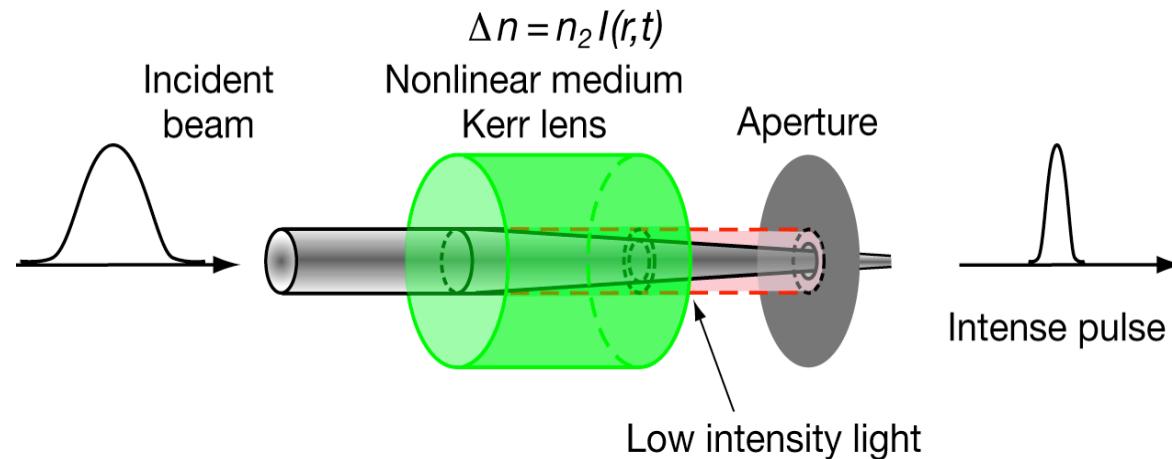
# Ultrashort pulse generation with modelocking



# Kerr Lens Modelocking (KLM)

First Demonstration: D. E. Spence, P. N. Kean, W. Sibbett, *Optics Lett.* **16**, 42, 1991

Explanation: U. Keller et al., *Optics Lett.* **16**, 1022, 1991



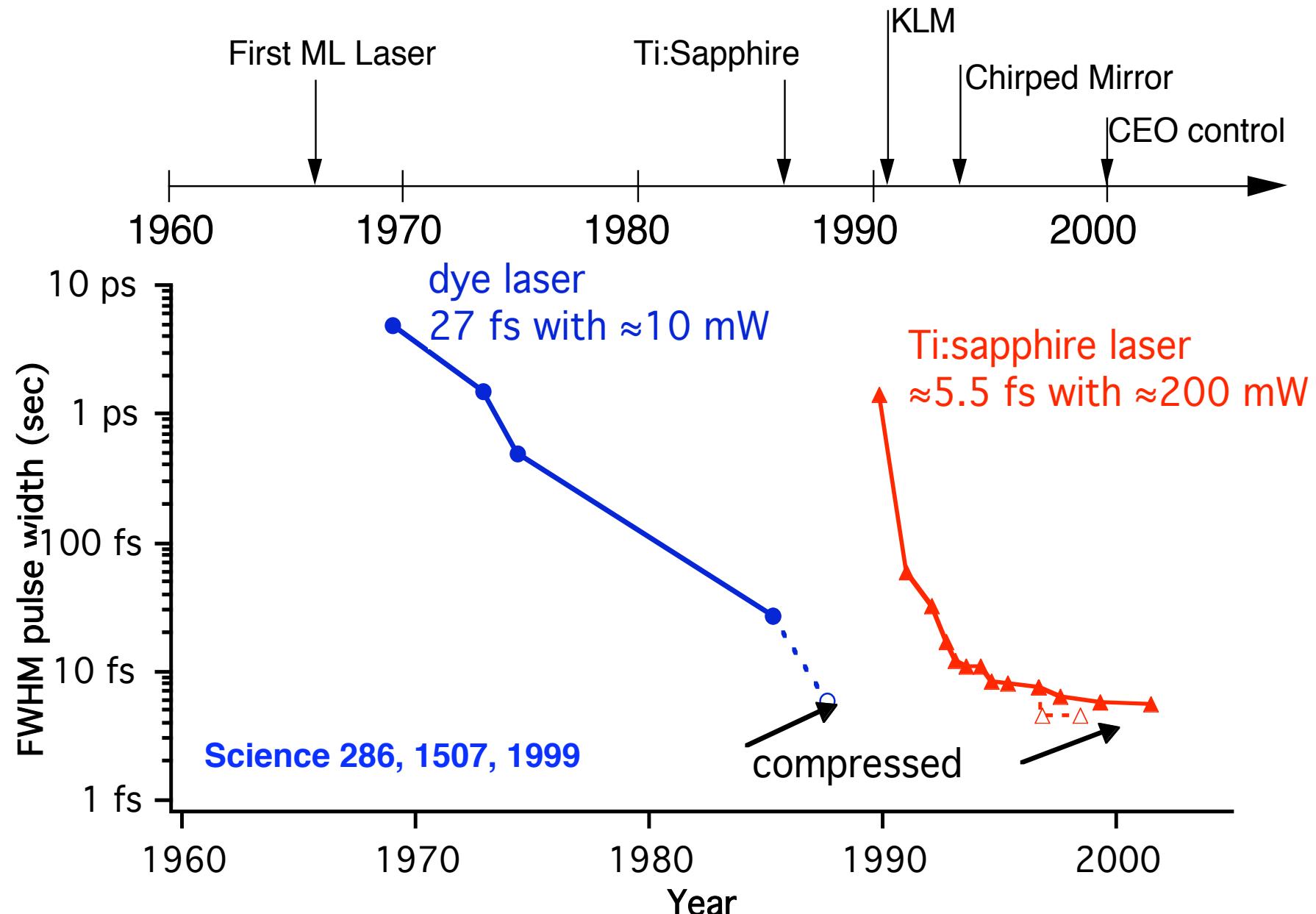
## Advantages of KLM

- very fast thus shortest pulses
- very broadband thus broader tunability

## Disadvantages of KLM

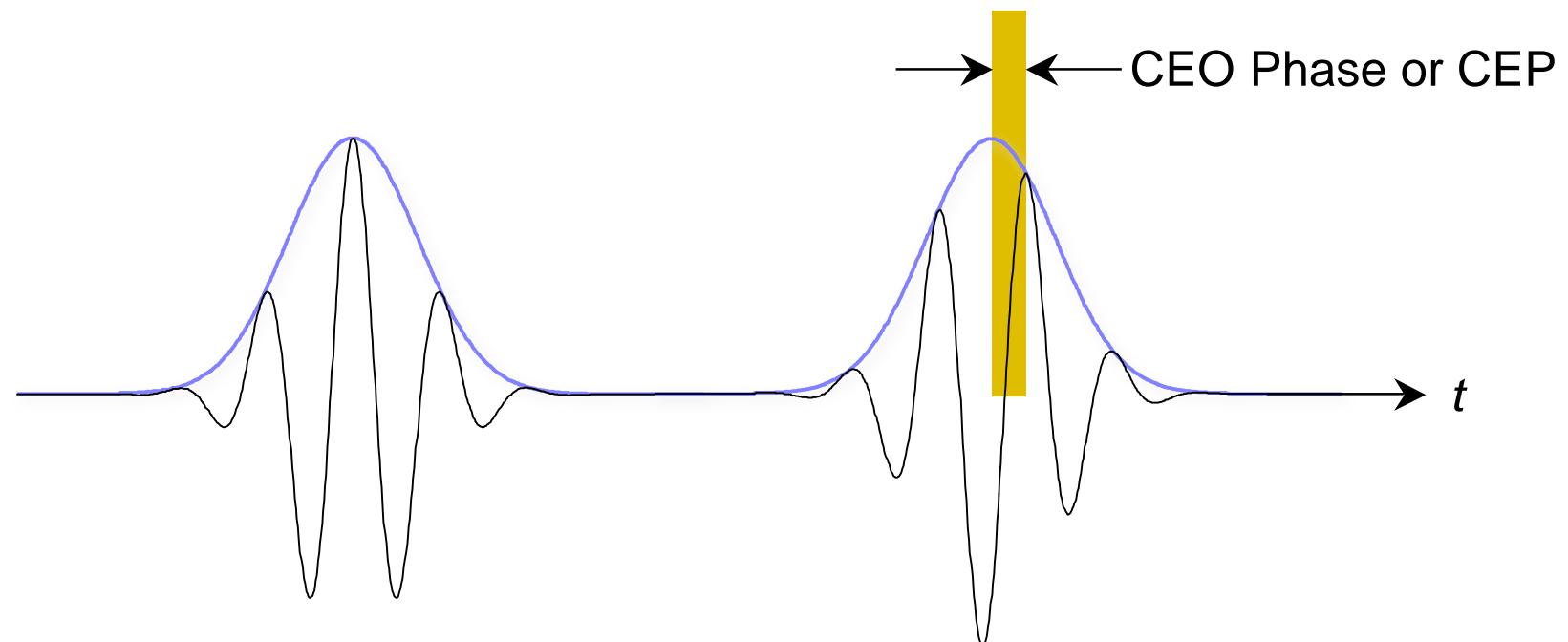
- not self-starting
- critical cavity adjustments  
(operated close to the stability limit)
- saturable absorber coupled to cavity design (limited application)

# Frontier: Ultrashort pulse generation



H.R. Telle, G. Steinmeyer, A. E. Dunlop, J. Stenger, D. H. Sutter, U. Keller  
*Appl. Phys. B* **69**, 327 (1999)

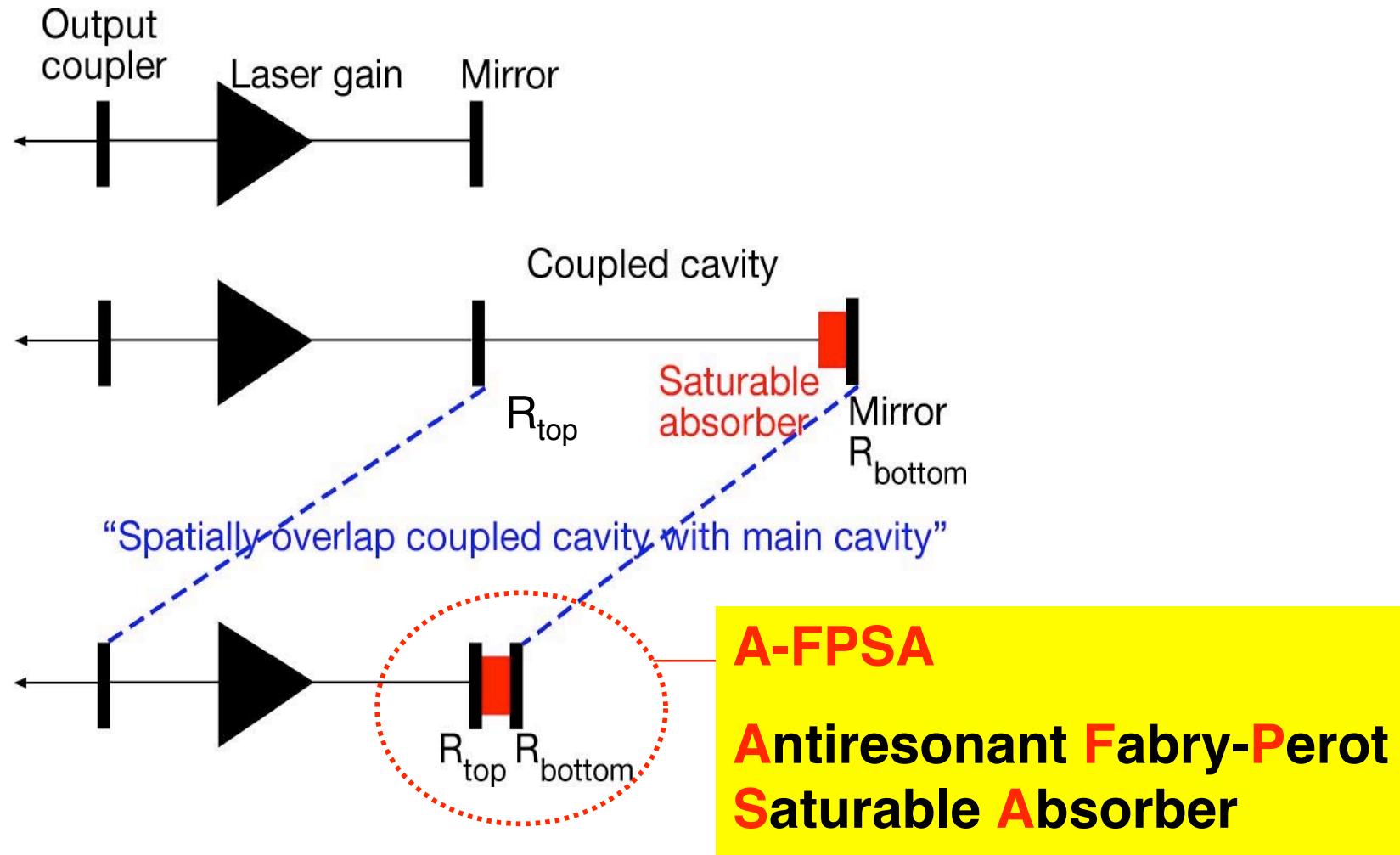
## Mode-locked Pulse Train



Controlled in laser oscillator

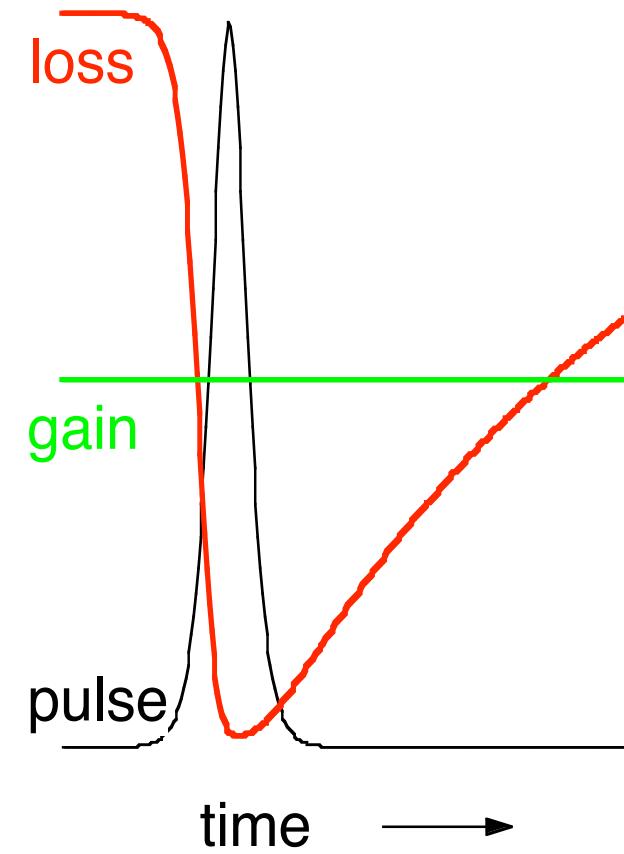
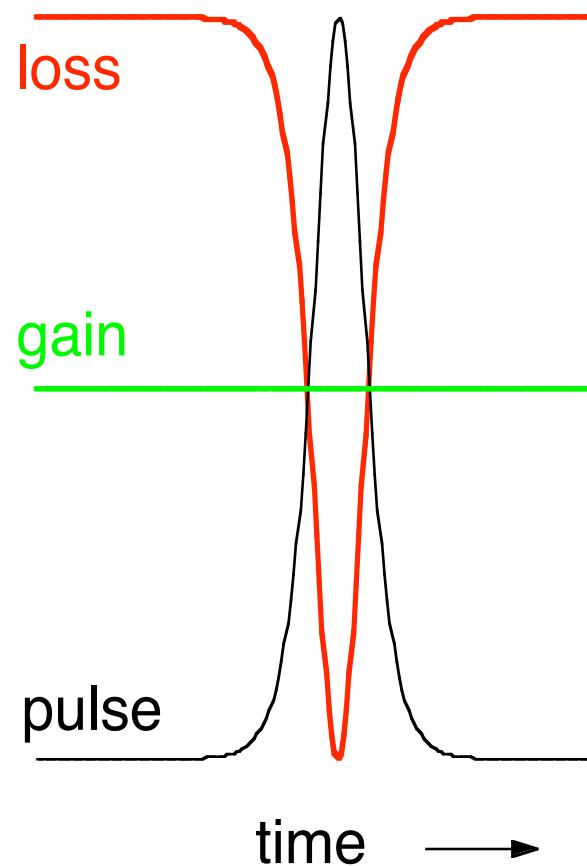
# Historical evolution for SESAMs

First intracavity saturable absorber - April 1, 1992



U. Keller et al., *Optics Lett.*, vol. 17, 505, 1992

# KLM vs. Soliton modelocking



## Kerr lens modelocking (KLM)

**Fast saturable absorber**

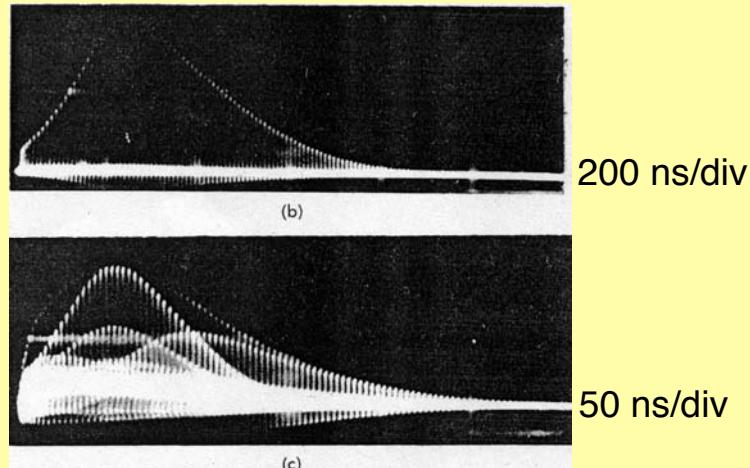
D. E. Spence, P. N. Kean, W. Sibbett  
*Opt. Lett.* **16**, 42, 1991

## Soliton modelocking

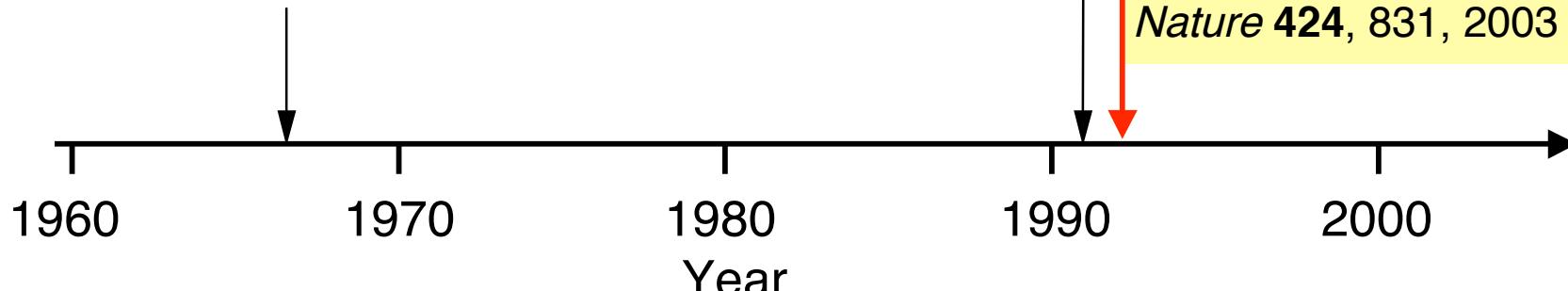
**“not so fast” saturable absorber**  
F. X. Kärtner, U. Keller,  
*Opt. Lett.* **20**, 16, 1995

# Ultrashort pulse generation with modelocking

A. J. De Maria, D. A. Stetser, H. Heynau  
*Appl. Phys. Lett.* **8**, 174, 1966



Nd:glass  
first passively modelocked laser  
**Q-switched modelocked**



**Flashlamp-pumped  
solid-state lasers**

**Q-switching instabilities  
continued to be a problem until 1992**

## SESAM

First passively modelocked  
(diode-pumped) solid-state laser  
without Q-switching

KLM

U. Keller et al.  
*Opt. Lett.* **17**, 505, 1992

*IEEE JSTQE* **2**, 435, 1996  
*Nature* **424**, 831, 2003

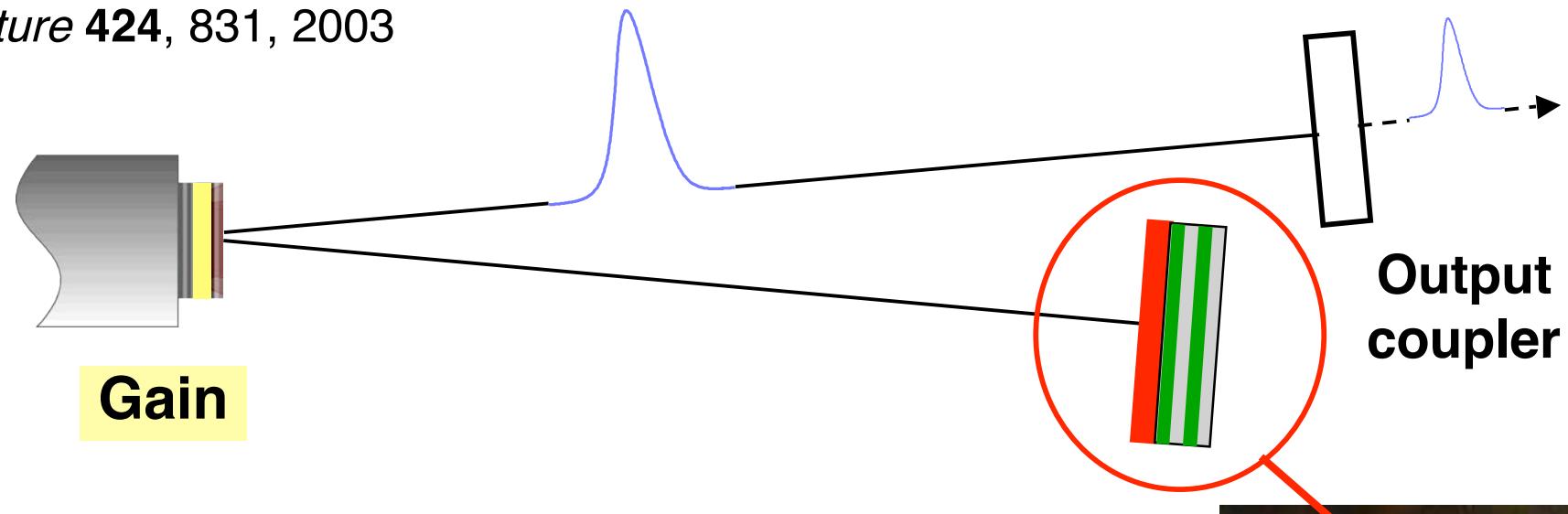
**Diode-pumped solid-state lasers  
(first demonstration 1963)**

U. Keller et al. *Opt. Lett.* **17**, 505, 1992

*IEEE JSTQE* **2**, 435, 1996

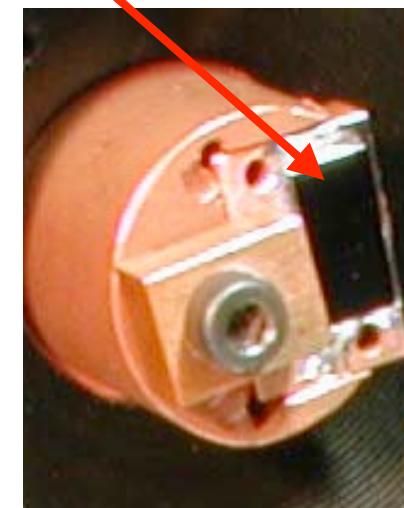
Progress in Optics **46**, 1-115, 2004

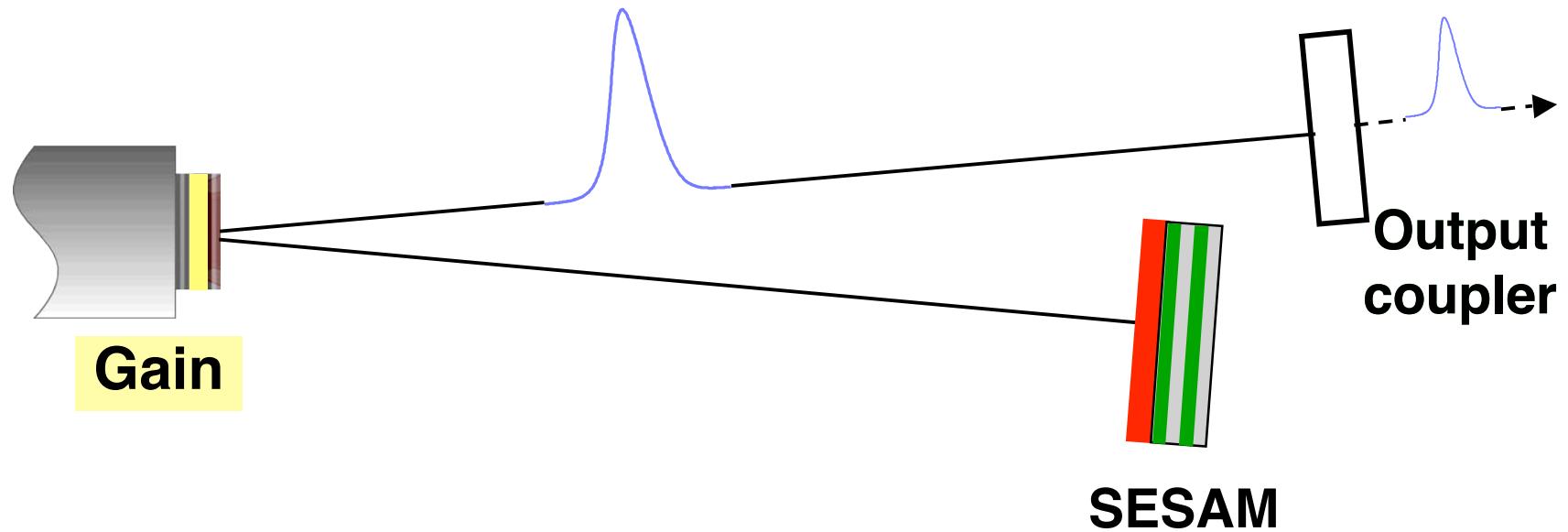
*Nature* **424**, 831, 2003



**SESAM**  
**SEmiconductor Saturable Absorber Mirror**

self-starting, stable, and reliable modelocking of  
diode-pumped ultrafast solid-state lasers





Short cavity length = high pulse repetition rate

Pulse repetition rate is given by the cavity round trip time.

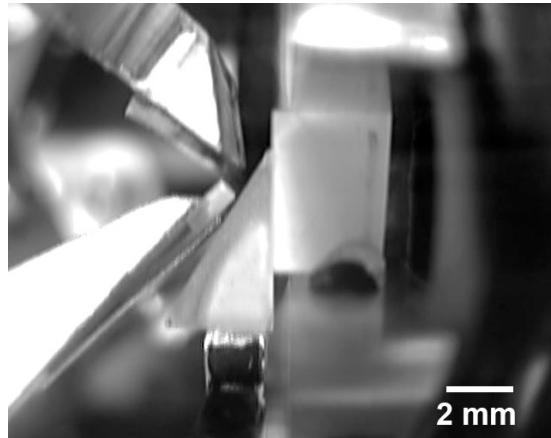
**1 GHz:** cavity round trip time 1 ns and a cavity length **15 cm**.

**1 THz:** cavity round trip time 1 ps and a cavity length **150 µm**.

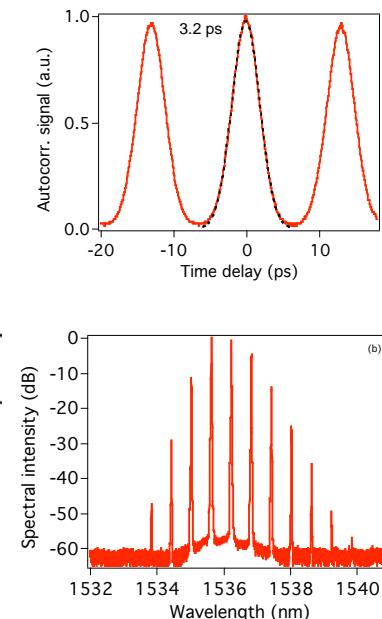
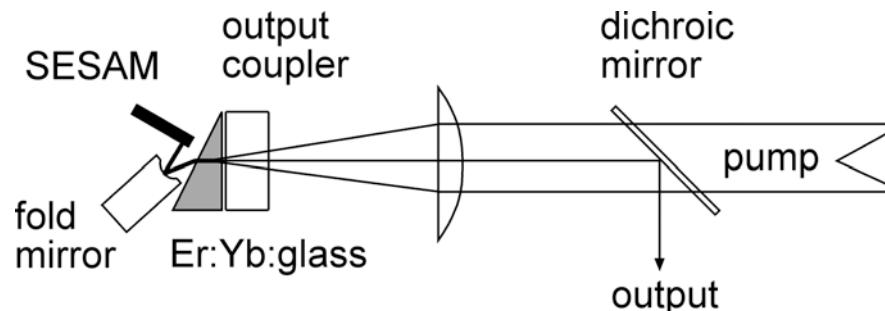
No high speed electronics needed.

# Compact high repetition rate lasers

## Diode-pumped solid-state lasers:

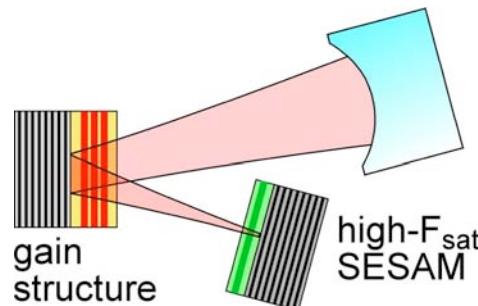


77-GHz SESAM modelocked Er:Yb:glass laser  
*Electron. Lett.* **43**, 32, 2007

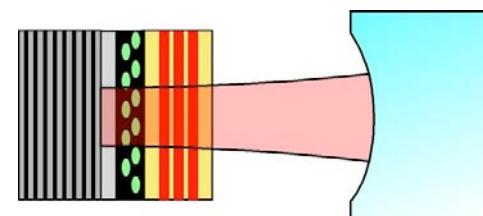


## (Optically pumped) semiconductor lasers:

*Physics Report* **429**, 67-120, 2006



Vertical integration of gain and absorber into the same wafer  
*Appl. Phys. B* **88**, 493, 2007



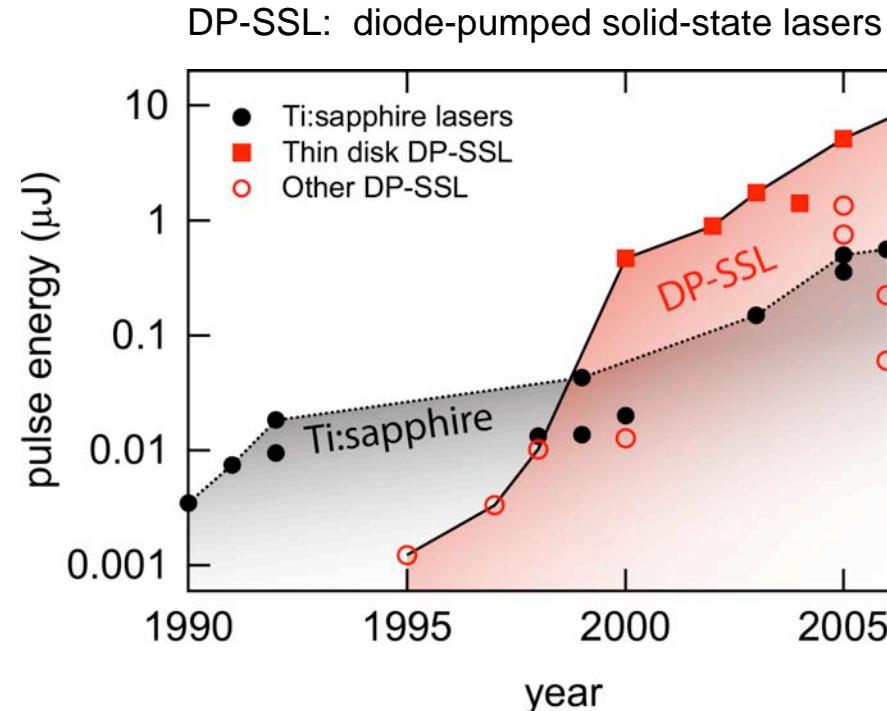
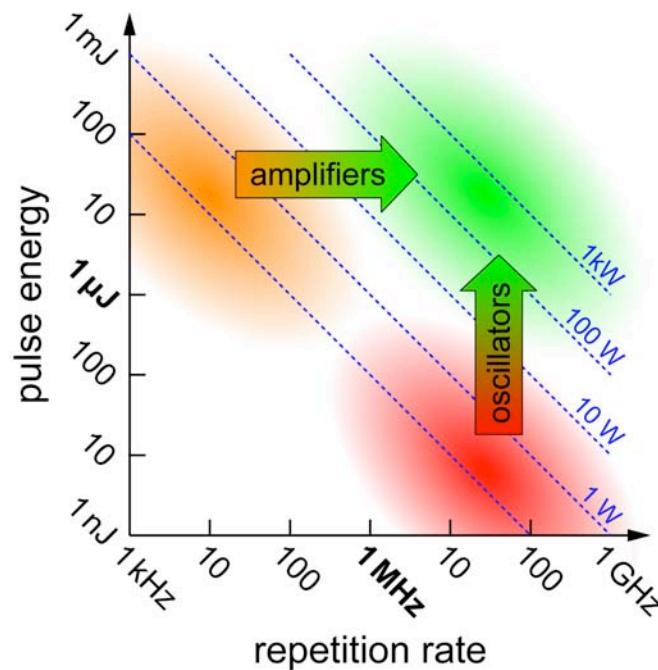
## Passively modelocked VECSEL

vertical external cavity surface emitting laser

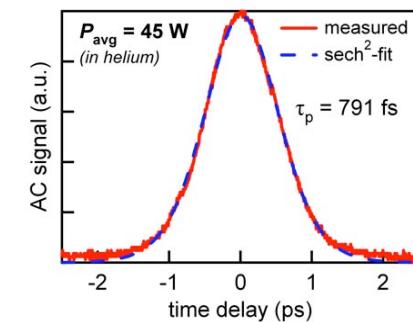
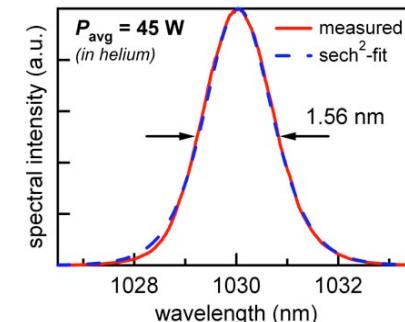
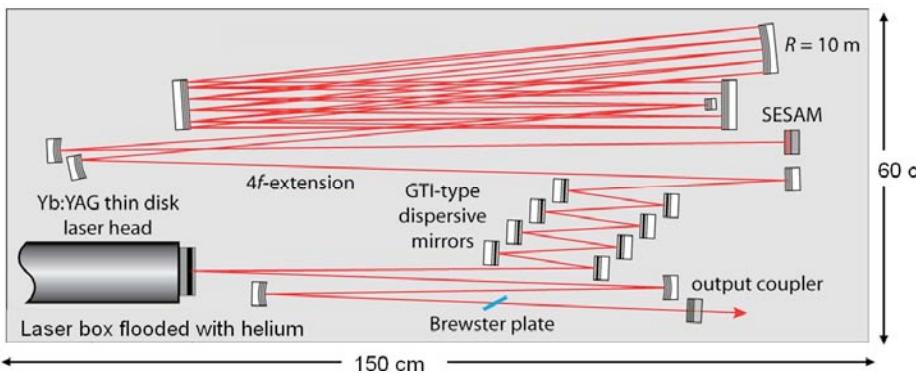
## MIXSEL

modellocked integrated external-cavity surface emitting laser

# High average power lasers



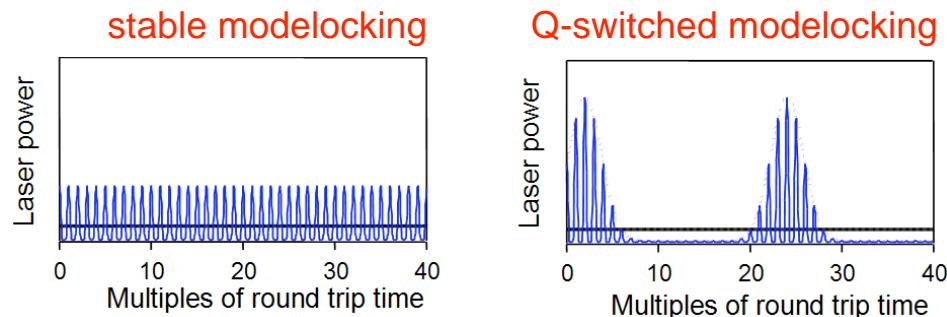
11  $\mu\text{J}$  pulse energy from a SESAM modelocked Yb:YAG thin disk laser:  
 >10'000 times improvement in diode-pumped lasers during the last 15 years



# Challenges for high power femtosecond oscillators

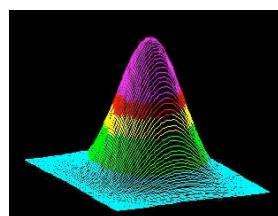
- Femtosecond pulse formation at high power levels
  - pulse forming element must sustain high intracavity power
  - prevent instabilities (e.g. Q-switched modelocking)

⇒ SESAM for pulse formation



- Laser technology operating at >100 W with Gaussian transverse beam profile ( $\text{TEM}_{00}$ )
  - prevent aberrations, provide cooling, ...
  - Resonator design for stability towards thermal lensing

⇒ Thin disk laser head  
for high power levels

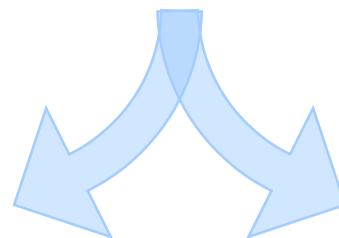


# Progress in high power modelocked lasers

First cw modelocked thin-disk laser (Yb:YAG):  
16 W, 730 fs, 0.5 MW

J. Aus der Au et al., *Opt. Lett.* **25**, 859 (2000)

Power scaling



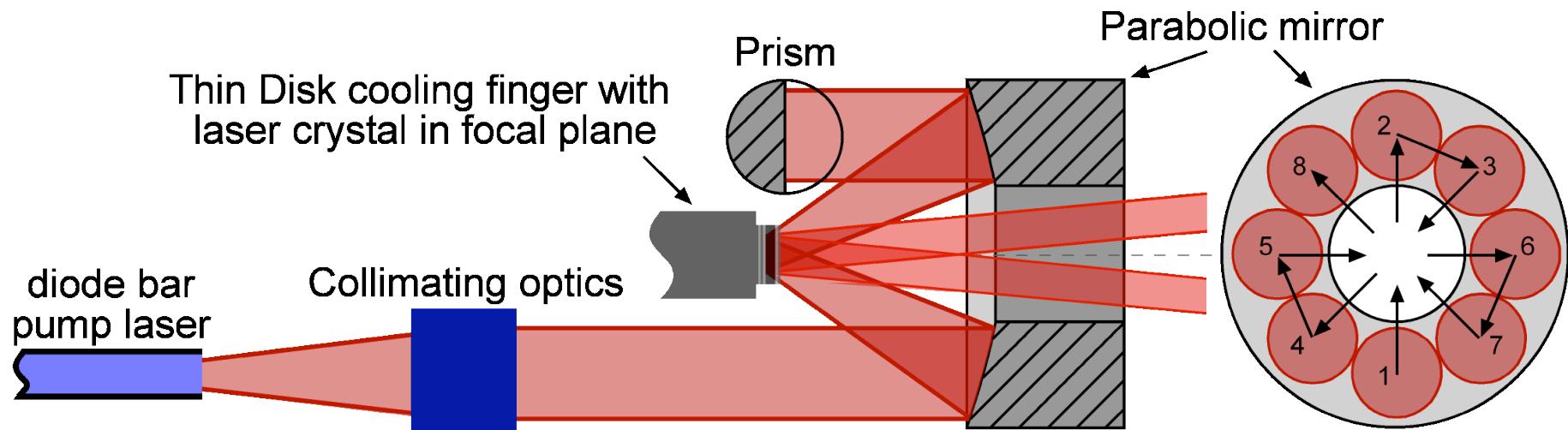
80 W, 705 fs, 1.75 MW

E. Innerhofer et al.,  
*Laser Phys. Lett.* **1**, 1 2004

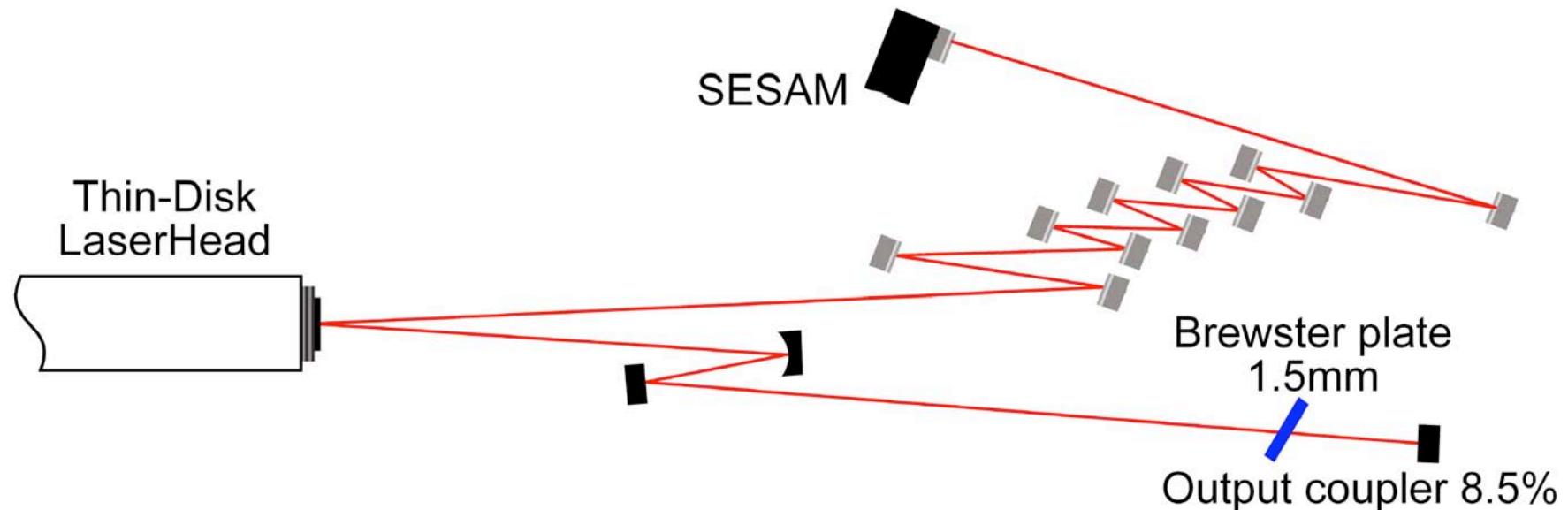
# Yb:YAG Thin-Disk Laser Head

A. Giesen et al., *Appl. Phys. B* **58**, 365, 1994  
constructed by TRUMPF Laser GmbH+Co. KG (Germany)

- Thickness of Yb:YAG disk: 100 µm (absorption length a few mm - need multiple passes of pump for efficient absorption)
- Diameter of pump spot: 2.8 mm
- Pump power: up to 370 W @ 940 nm
- 16 passes of pump radiation through disk

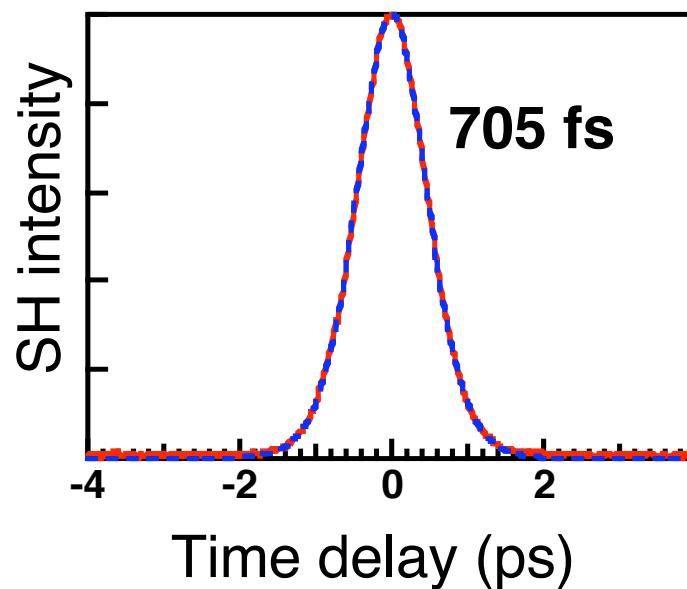


# Thin disk laser: 57-MHz setup

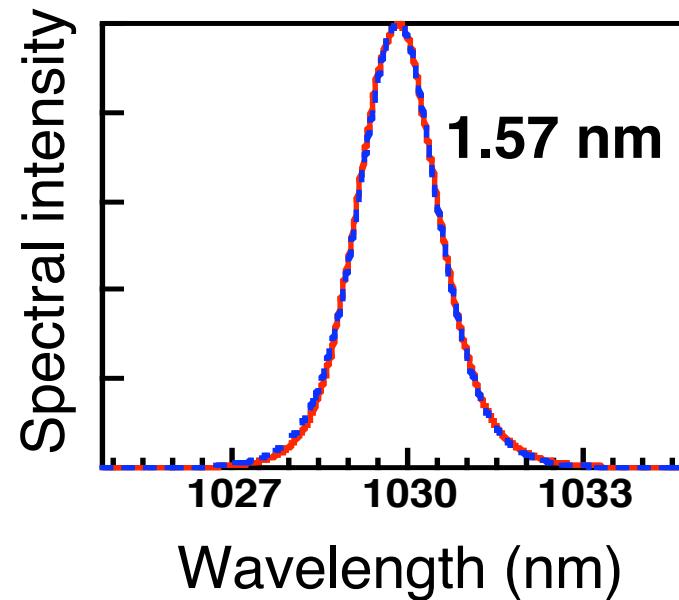


- Thin disk **as folding mirror**
- SESAM and output coupler **as end mirror**
- Brewster plate **for linear polarization**
- **Negative group delay dispersion from GTI-type dispersive mirrors**

## Autocorrelation



## Optical spectrum

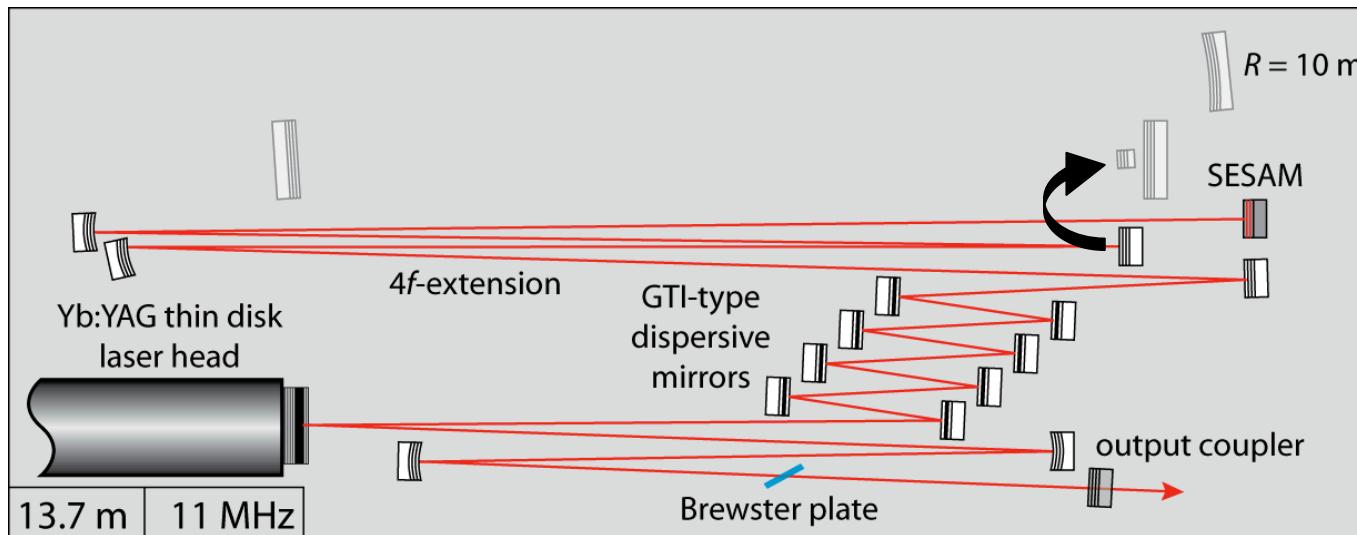


$$\begin{aligned} P_{\text{avg}} &= 80 \text{ W} \\ \tau_p &= 705 \text{ fs} \\ f_{\text{rep}} &= 57 \text{ MHz} \end{aligned}$$

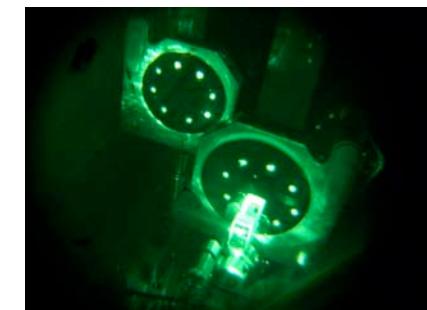
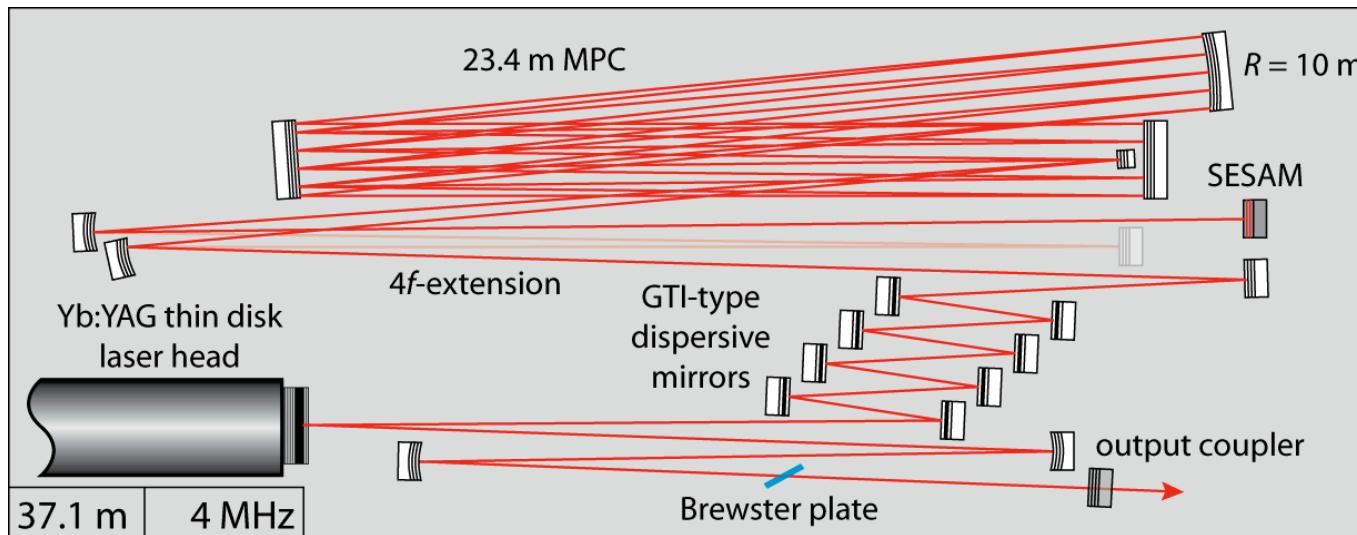
$$\begin{aligned} E_p &= 1.4 \mu\text{J} \\ P_{\text{peak}} &= 1.75 \text{ MW} \\ \Delta\nu\tau_p &= 0.32 \end{aligned}$$

First modelocked (ML) thin-disk, 16 W: *Optics Lett.* **25**, 859, 2000  
60 W ML Thin Disk: E. Innerhofer et al., *Optics Lett.* **28**, 367, 2003  
80 W ML Thin Disk: F. Brunner et al., *Optics Lett.* **29**, 1921, 2004

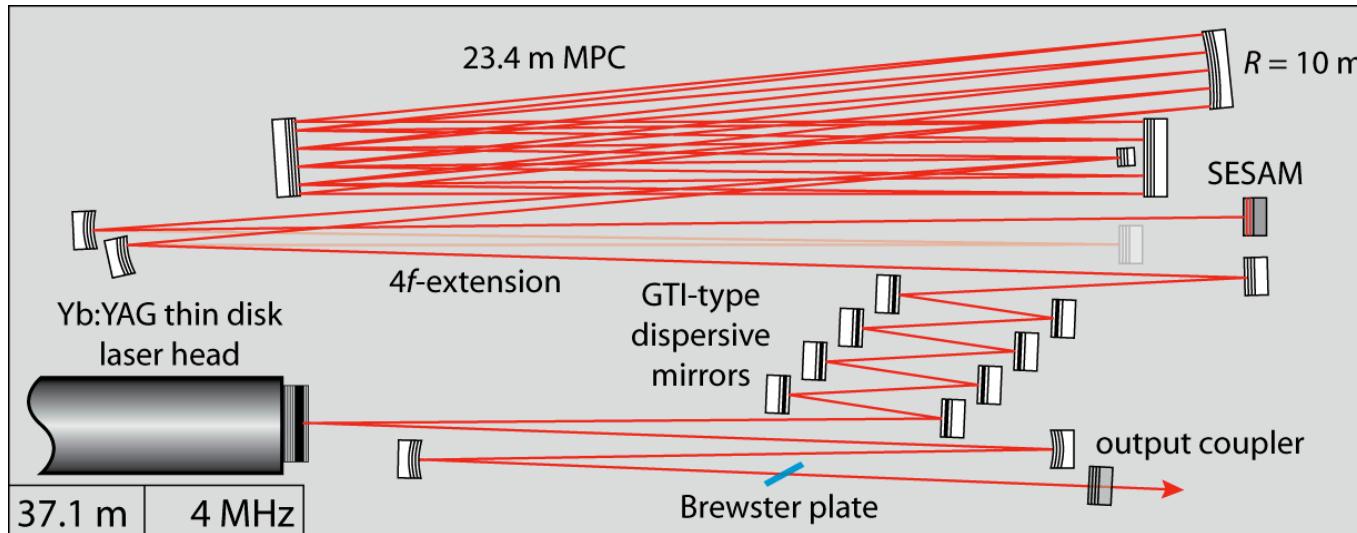
# Laser setup and results



# Laser setup and results



# Laser setup and results



## Yb:YAG laser head

- $\approx 9\%$  Yb-doped YAG
- $d_{\text{disk}} \approx 200 \mu\text{m}$ ,  $w_{\text{pump}} \approx 1.4 \text{ mm}$
- $P_{\text{pump}}$  up to 230 W @ 940 nm  
(TGSW, Stuttgart, Germany)

## SESAM

- $F_{\text{sat}} \approx 115 \mu\text{J}/\text{cm}^2$
- $\Delta R \approx 0.5 \%$

## 13 dispersive mirrors

- $\approx -550/1000 \text{ fs}^2 \text{ GDD per bounce}$
- $\approx -20000 \text{ fs}^2 \text{ GDD per roundtrip}$

## Brewster plate (SPM + linear pol.)

- 1 mm thick fused silica

## Output coupler

- 10% at 1030 nm

## in air atmosphere

no stable mode locking achieved → instabilities & multiple pulses

**in air atmosphere**

no stable mode locking achieved → instabilities & multiple pulses

↓ helium flooding ↓

**in helium atmosphere**

$$\begin{aligned} P_{\text{avg}} &= 45 \text{ W} \\ f_{\text{rep}} &= 4 \text{ MHz} \end{aligned}$$



$$E_p = 11.3 \text{ } \mu\text{J}$$

pulse energy limited by:

- **strong saturation of the SESAM**
- **air-tightness of the helium box**

## in air atmosphere

no stable mode locking achieved → instabilities & multiple pulses

↓ helium flooding ↓

## in helium atmosphere

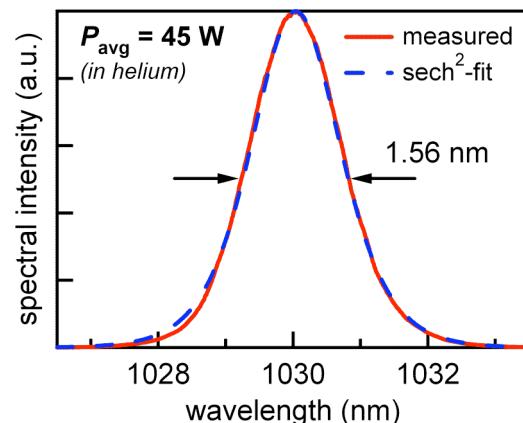
$$\begin{aligned} P_{\text{avg}} &= 45 \text{ W} \\ f_{\text{rep}} &= 4 \text{ MHz} \end{aligned}$$



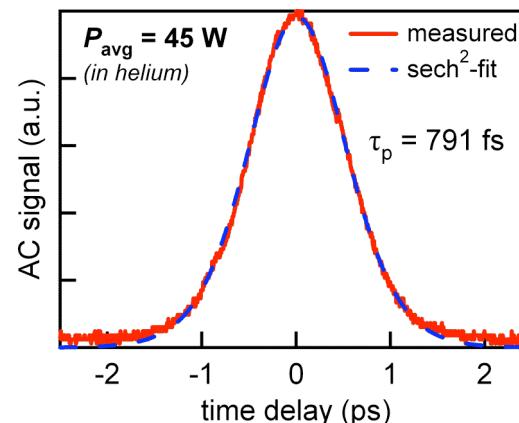
$$E_p = 11.3 \text{ } \mu\text{J}$$

pulse energy limited by:

- strong saturation of the SESAM
- air-tightness of the helium box



$$\begin{aligned} \lambda &= 1030 \text{ nm} \\ \Delta\lambda &= 1.56 \text{ nm} \end{aligned}$$



$$\begin{aligned} M^2 &= 1.1 \\ P_{\text{peak}} &= 12.5 \text{ MW} \end{aligned}$$

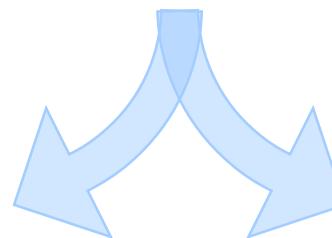
$$\begin{aligned} \tau_p &= 791 \text{ fs} \\ \tau_p \cdot \Delta\nu &= 0.35 \text{ (ideal 0.315)} \end{aligned}$$

# Progress in high power modelocked lasers

First cw modelocked thin-disk laser (Yb:YAG):  
16 W, 730 fs, 0.5 MW

J. Aus der Au et al., *Opt. Lett.* **25**, 859 (2000)

Power scaling



Pulse duration reduced  
with different laser  
material Yb:KYW

80 W, 705 fs, 1.75 MW

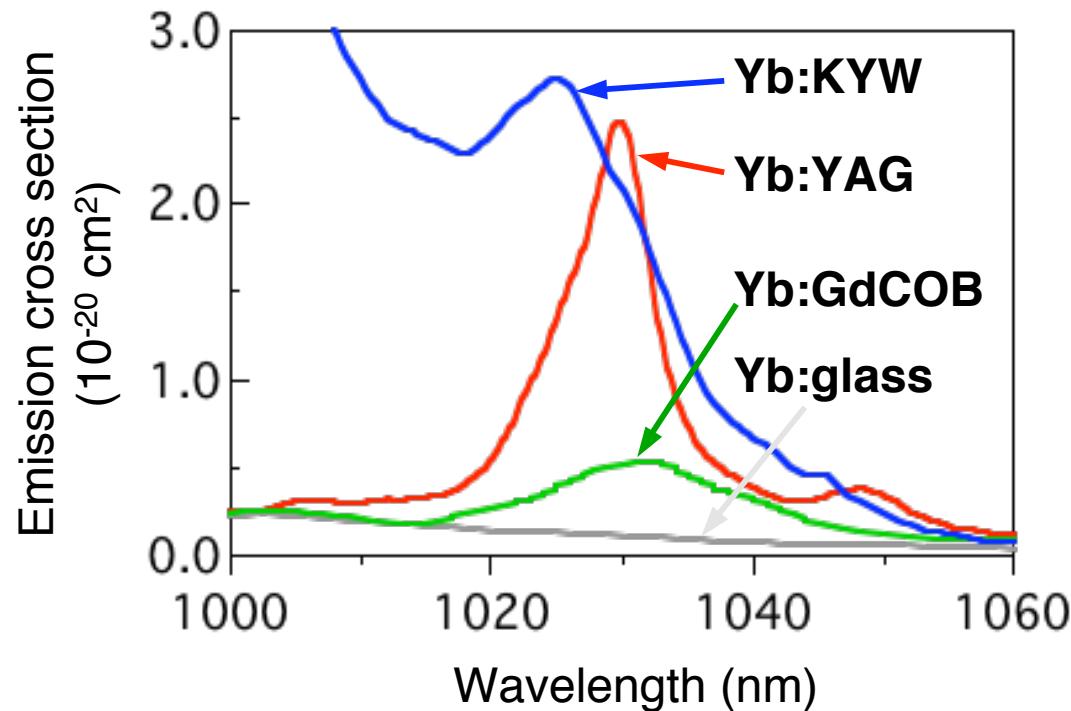
E. Innerhofer et al.,  
*Laser Phys. Lett.* **1**, 1 2004

22 W, 240 fs, 3.3 MW

F. Brunner et al.,  
*Opt. Lett.* **27**, 1162 (2002)

# Yb-doped tungstate laser: Yb:KYW {Yb:KY(WO<sub>4</sub>)<sub>2</sub>}

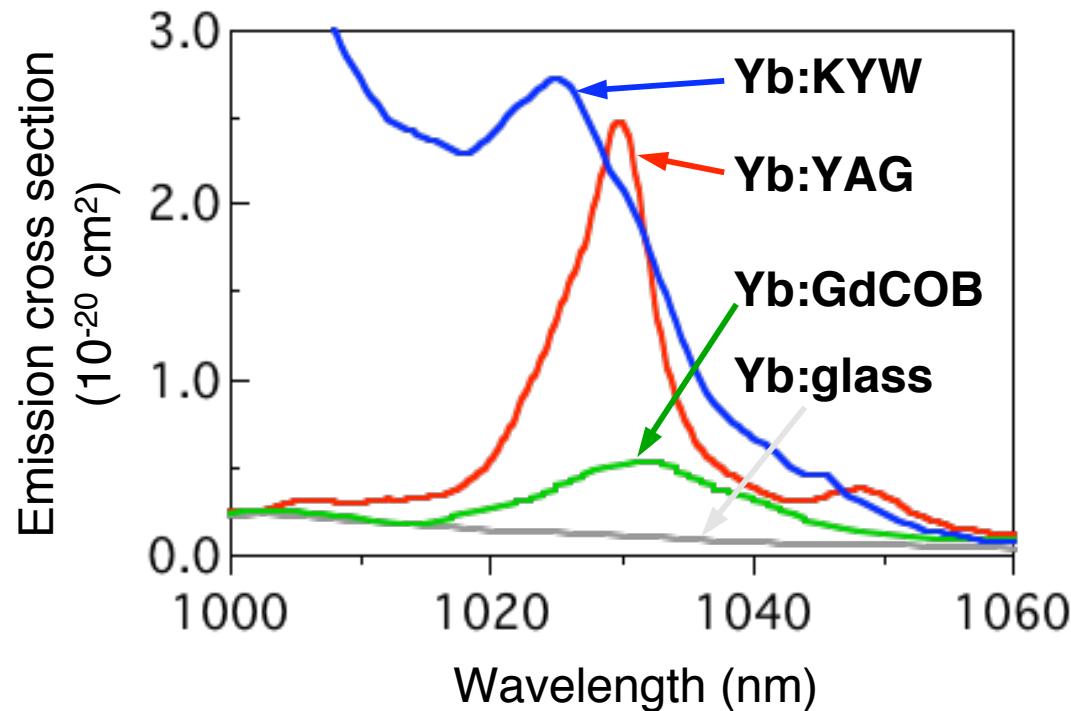
N. V. Kuleshov et al., *Opt. Lett.* **22**, 1317 (1997)



- broad emission spectrum → potential for  $\approx 100\text{-fs}$  pulse
- large emission cross section → lower tendency for QML
- small quantum defect (4%) → reduced heating effects
- good thermal conductivity,  $\kappa = 3.3 \text{ W/Km}$  → efficient cooling

# Yb-doped tungstate laser: Yb:KYW {Yb:KY(WO<sub>4</sub>)<sub>2</sub>}

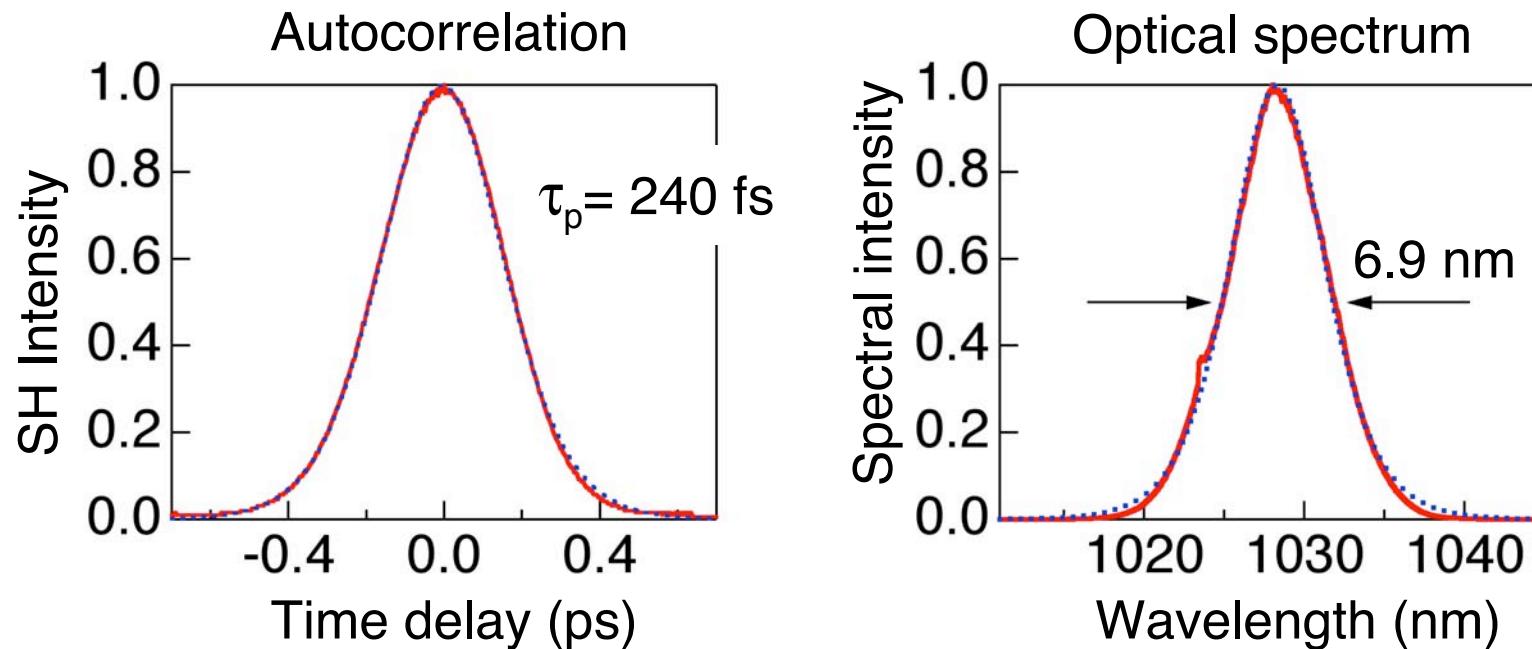
N. V. Kuleshov et al., *Opt. Lett.* **22**, 1317 (1997)



- broad emission spectrum → potential for  $\approx 100\text{-fs}$  pulse
- large emission cross section → lower tendency for QML
- small quantum defect (4%) → reduced heating effects
- good thermal conductivity,  $\kappa = 3.3 \text{ W/Km}$  → efficient cooling

# High power SESAM modelocked Yb:KYW laser

F. Brunner et al., *Opt. Lett.* **27**, 1162 (2002)



$$P_{\text{avg}} = 22 \text{ W}$$

$$\tau_p = 240 \text{ fs}$$

$$f_{\text{rep}} = 25 \text{ MHz}$$

$$M^2 = 1.1$$

$$E_p = 0.9 \mu\text{J}$$

$$P_{\text{peak}} = 3.3 \text{ MW}$$

linear polarisation

$$P_{\text{pump}} = 100 \text{ W}$$

# Progress in high power modelocked lasers

First cw modellocked thin-disk laser (Yb:YAG):  
16 W, 730 fs, 0.5 MW  
J. Aus der Au et al., *Opt. Lett.* **25**, 859 (2000)

Power scaling

80 W, 705 fs, 1.75 MW  
E. Innerhofer et al.,  
*Laser Phys. Lett.* **1**, 1 2004

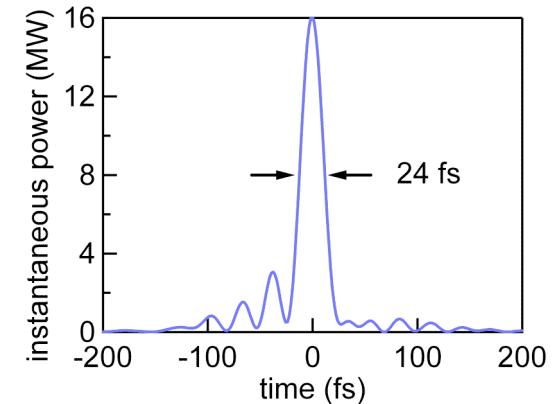
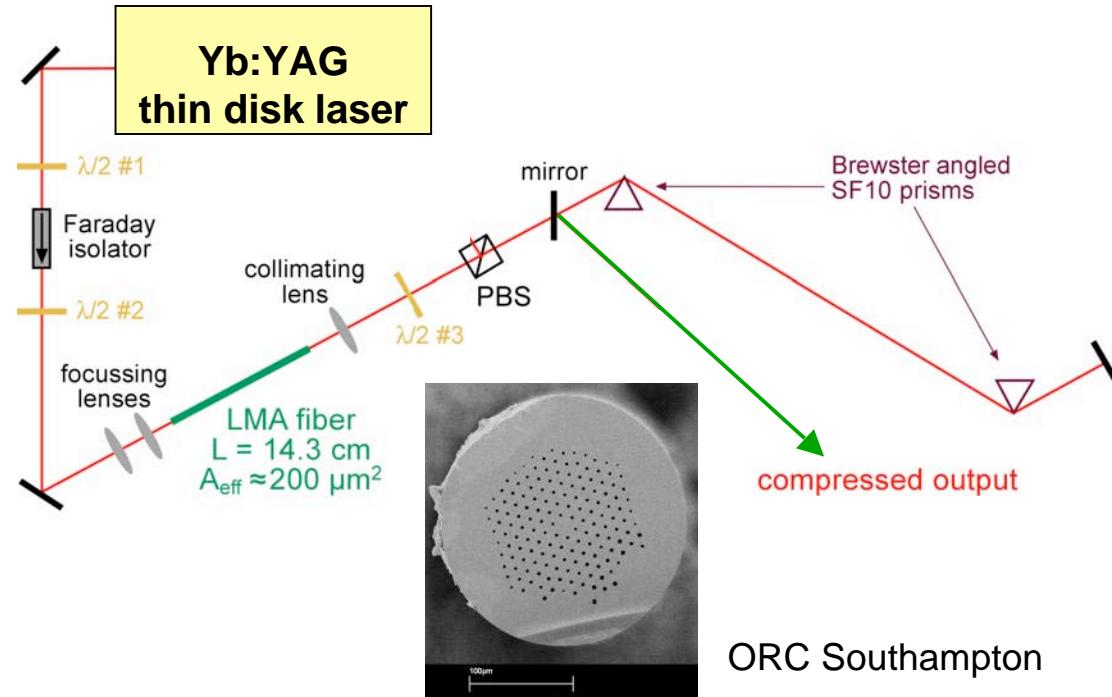
Pulse duration reduced  
with different laser  
material Yb:KYW

22 W, 240 fs, 3.3 MW  
F. Brunner et al.,  
*Opt. Lett.* **27**, 1162 (2002)

even shorter pulse duration?

No laser material

# Fiber compression system



**Incident on fiber**

$$P_{\text{peak}} = 1.2\text{ MW}$$

$$\tau_p = 760\text{ fs}$$

$$E_{p\text{-inc}} = 1\text{ }\mu\text{J}$$

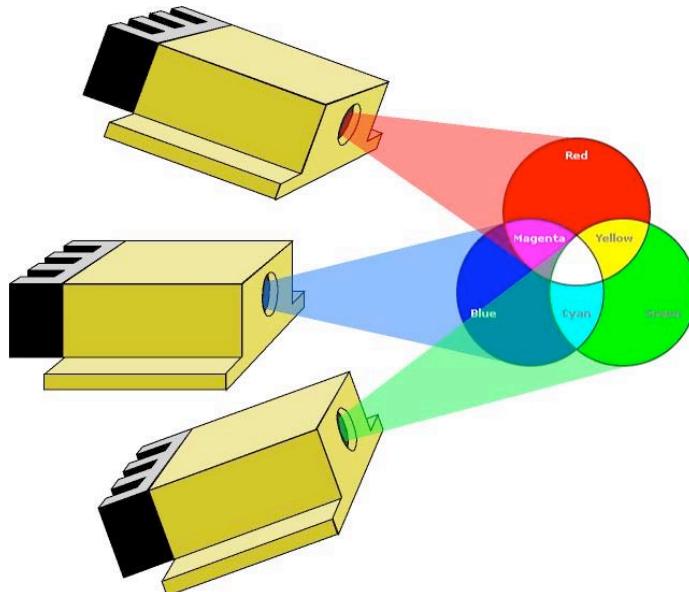
**After compression**

$$P_{\text{peak}} = 16\text{ MW}$$

$$\tau_p = 24\text{ fs}$$

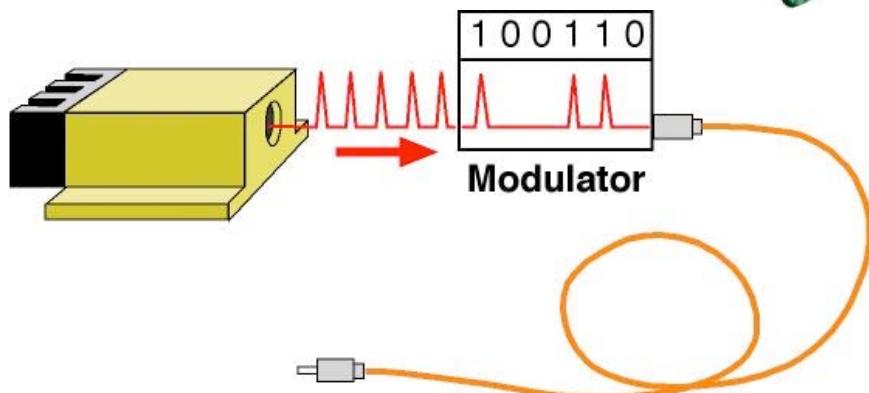
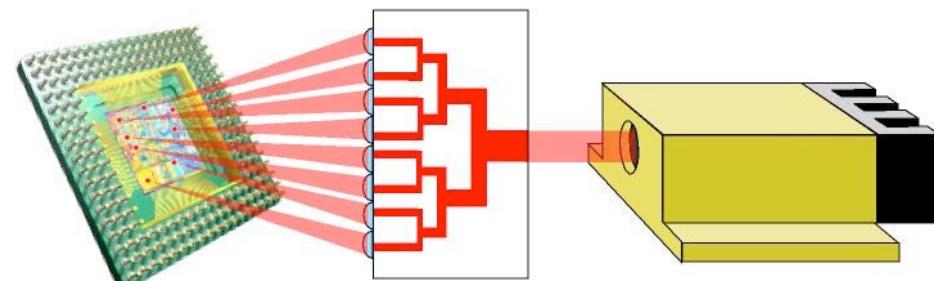
$$E_{p\text{-inc}} = 0.6\text{ }\mu\text{J}$$

T. Südmeyer et al, Optics Lett. **28**, 1951 (2003), E. Innerhofer, TuA3, ASSP 2004

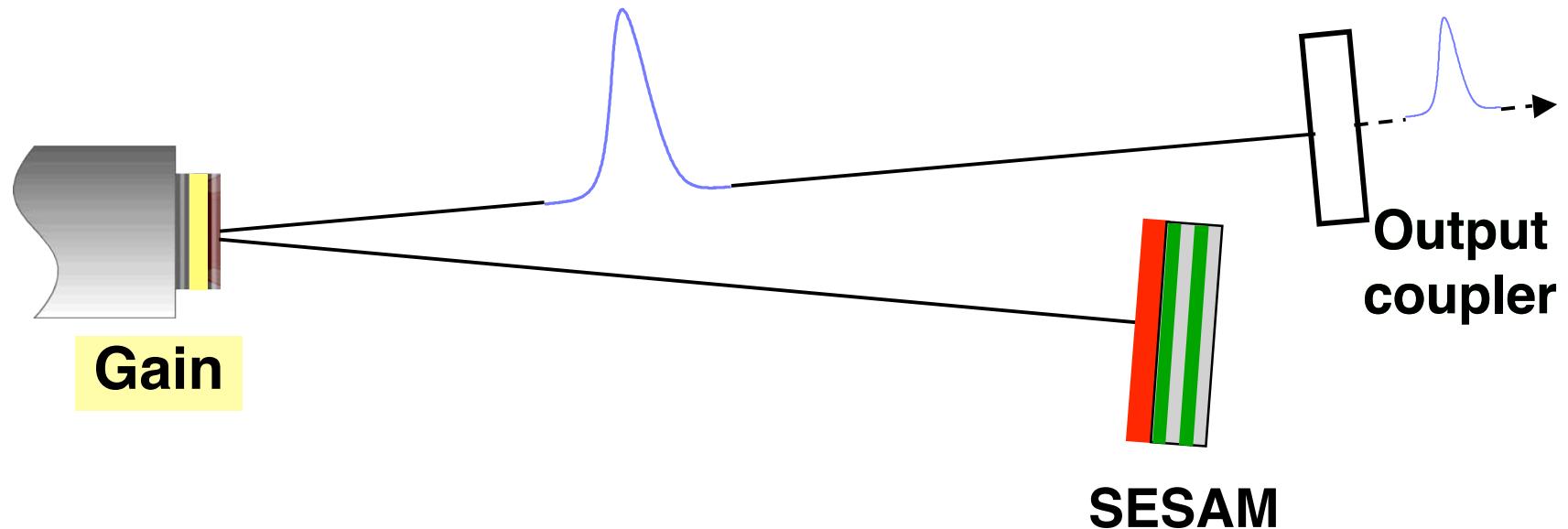


Frequency doubling,  
RGB Systems

Optical Clocking



Telecommunications



Short cavity length = high pulse repetition rate

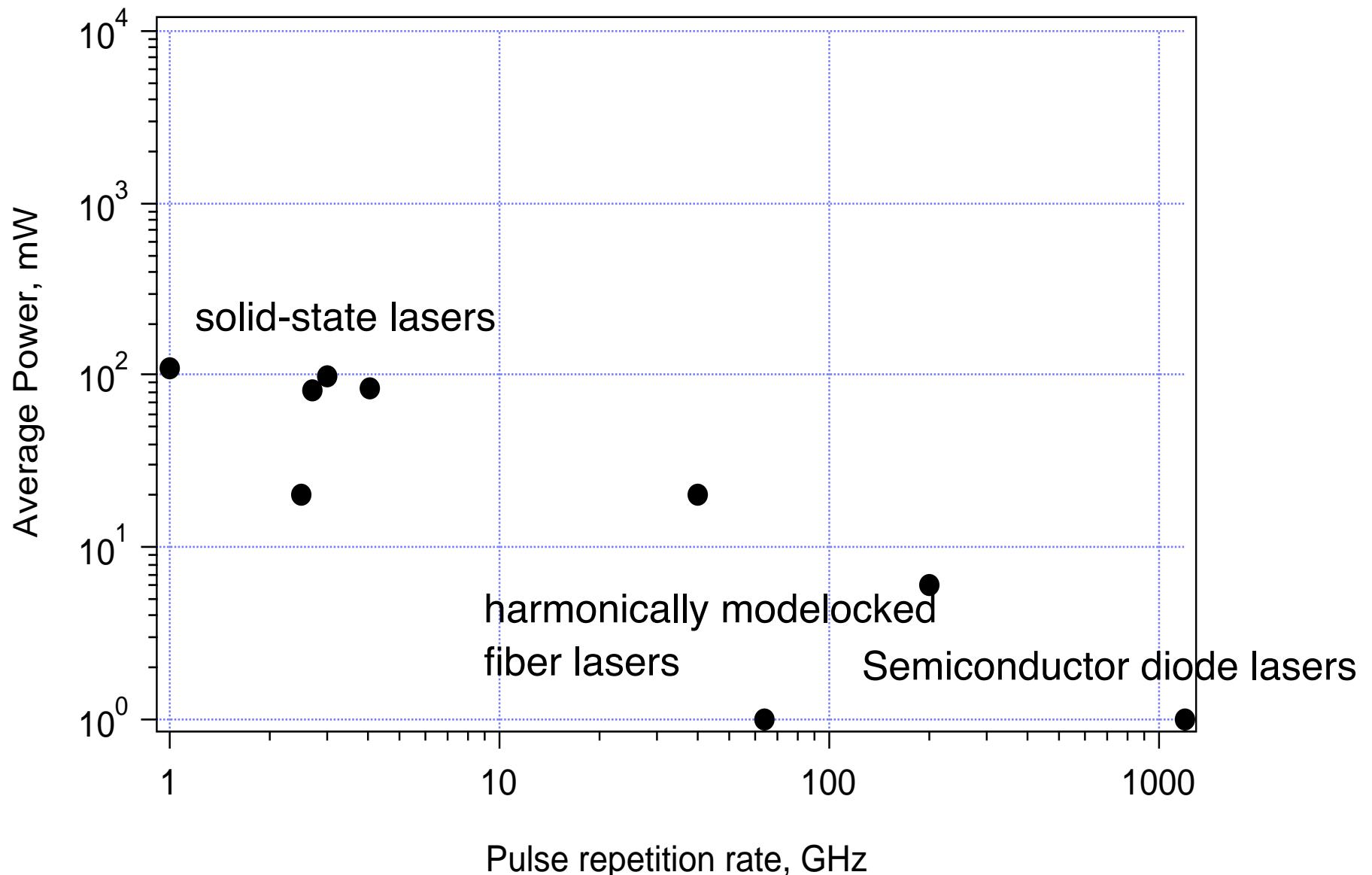
Pulse repetition rate is given by the cavity round trip time.

**1 GHz:** cavity round trip time 1 ns and a cavity length **15 cm**.

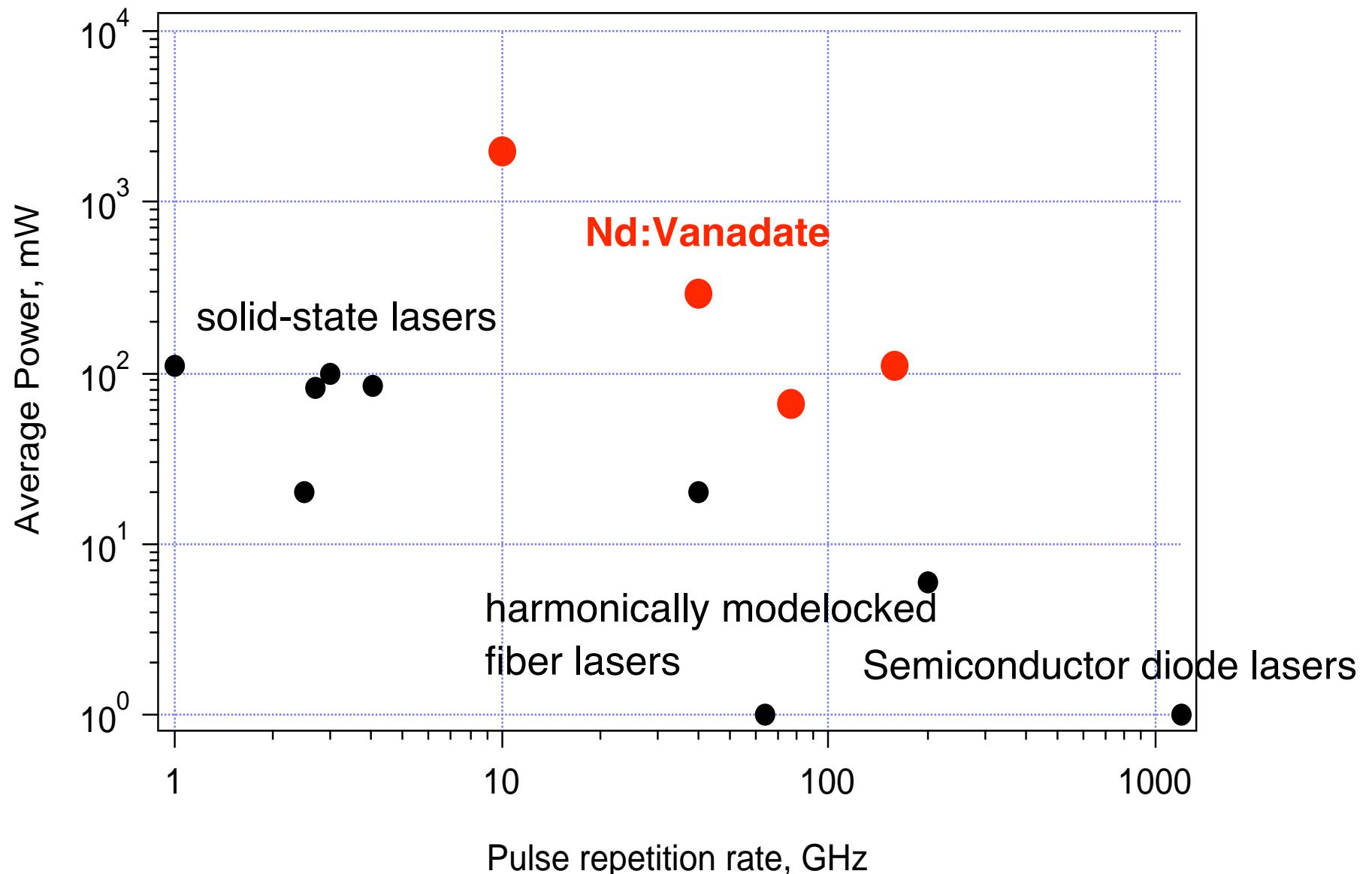
**1 THz:** cavity round trip time 1 ps and a cavity length **150 μm**.

No high speed electronics needed.

# High pulse repetition rate sources

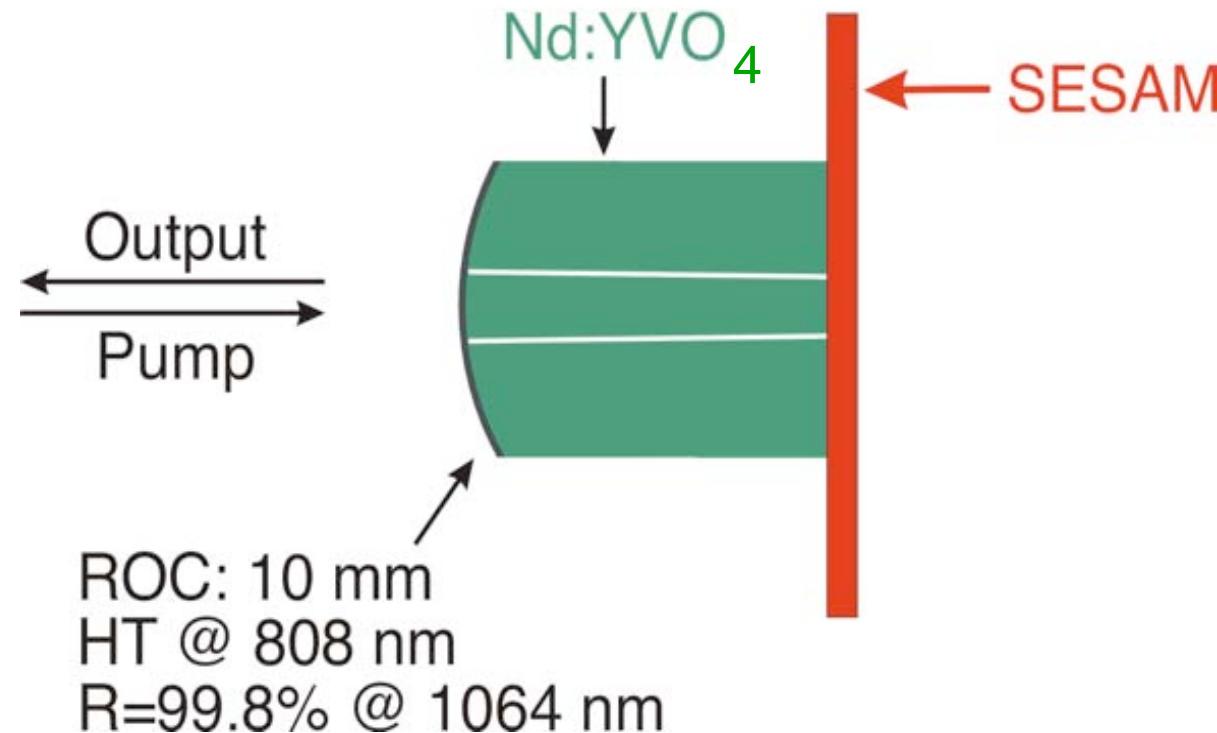


# High pulse repetition rate sources



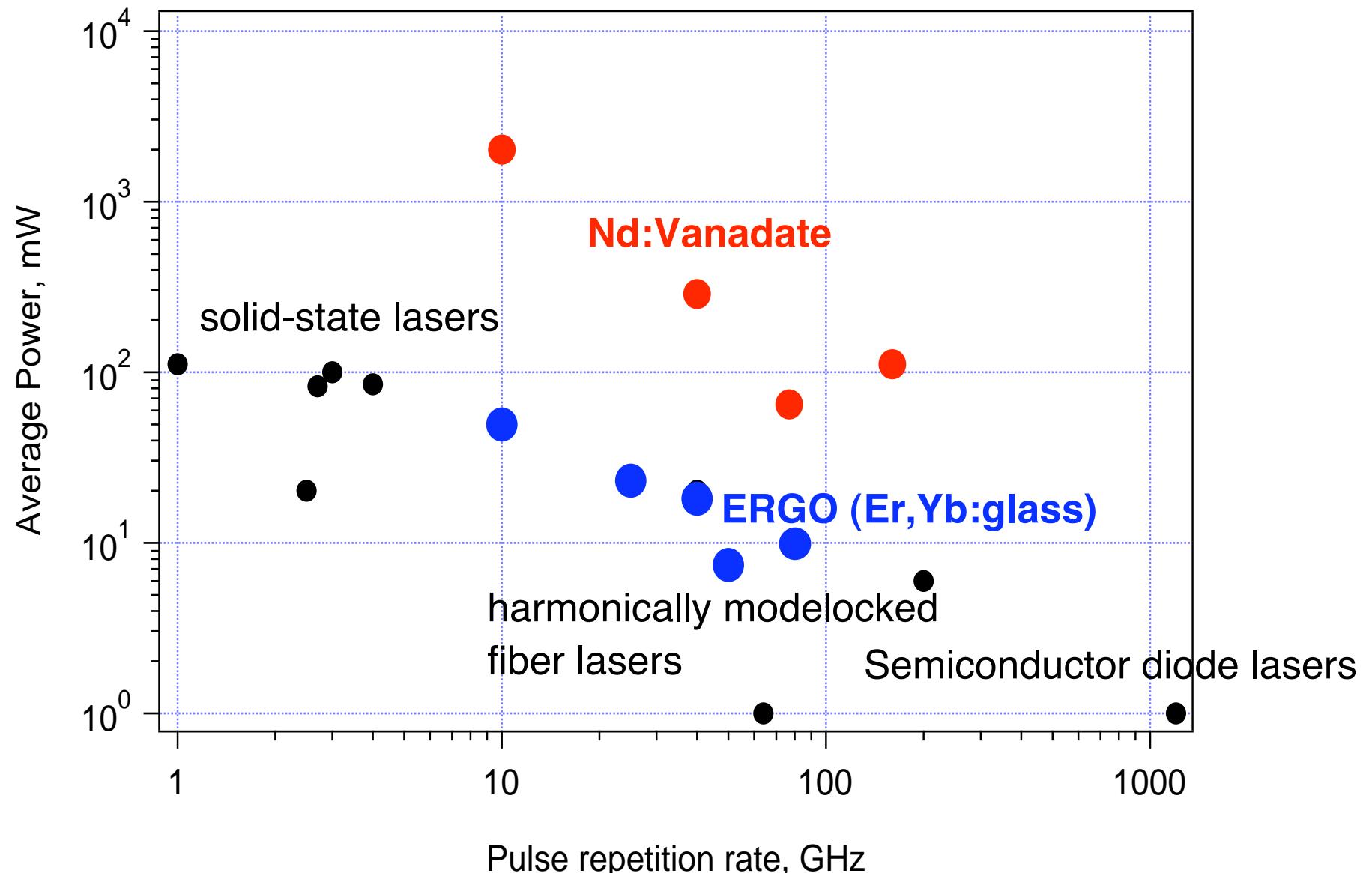
# Quasi-Monolithic Cavity Setup

*L. Krainer et al., Electron. Lett. **35**, 1160, 1999 (29 GHz)  
APL **77**, 2104, 2000 (up to 59 GHz), Electron. Lett. **36**, 1846, 2000 (77 GHz)  
IEEE J. Quant. Electron. **38**, 1331, 2002 (10 to 160 GHz)*

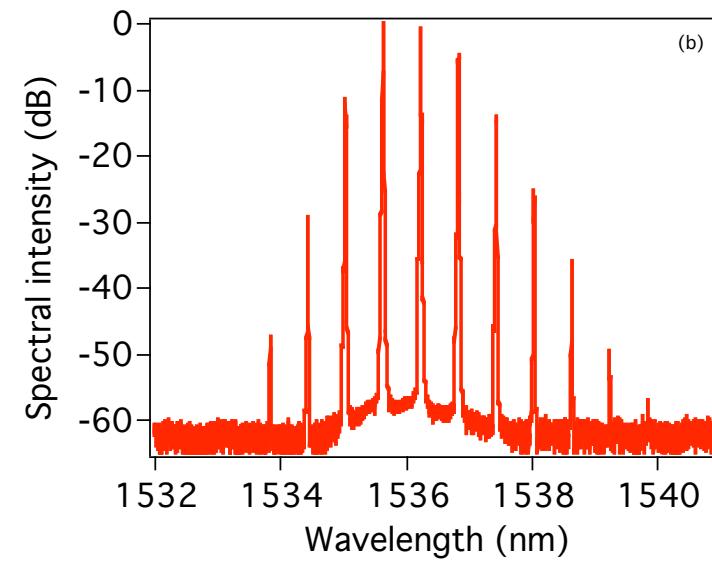
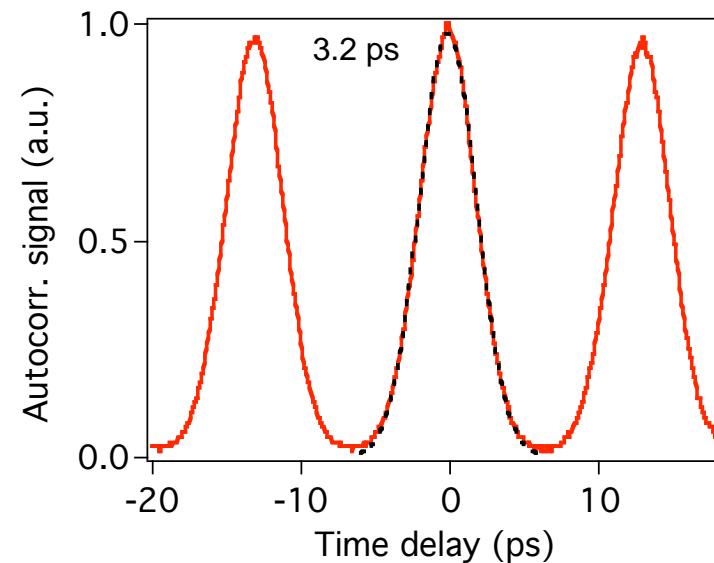
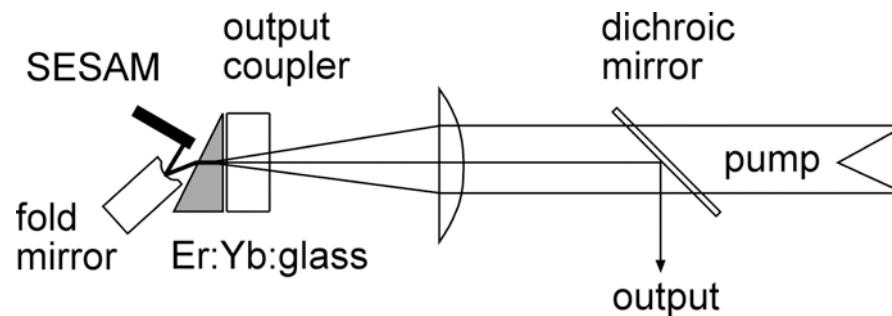
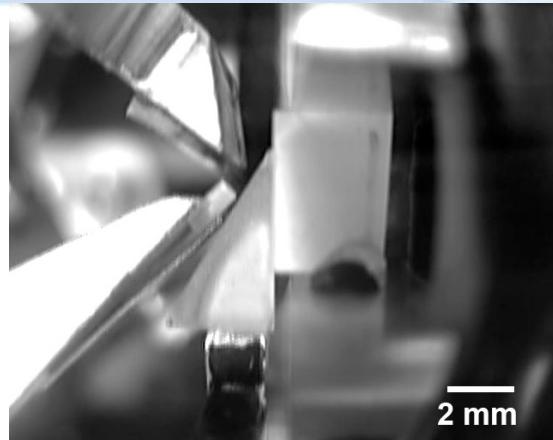


- Crystal lengths: 440 μm - 2.3 mm (FSR ~ 160 - 29 GHz)
- Nd:YVO<sub>4</sub> doping: 3 % (90 μm absorption length)

# High pulse repetition rate sources



# All-optical 77-GHz pulse generation

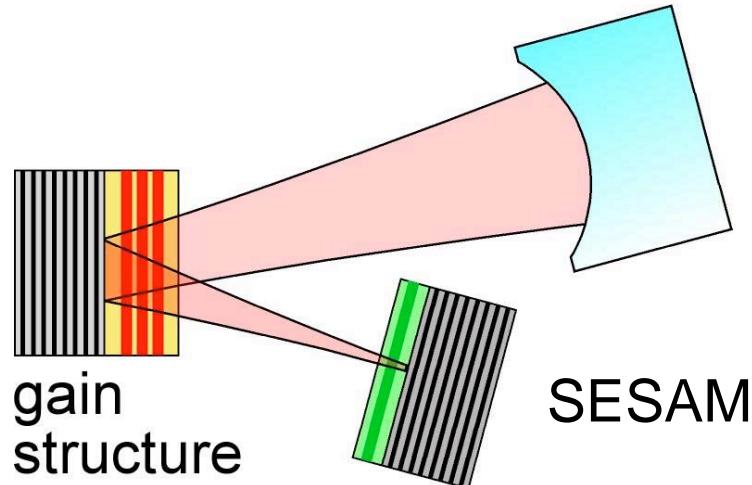


- 77 GHz at 1538.8 nm (standing wave cavity length 1.9 mm)
- 3.2 ps with average output power of 10 mW, TBP 0.37 (nearly transform limited)

S. C. Zeller et al, *Electron. Lett.*, vol. 43, pp. 32, 2007

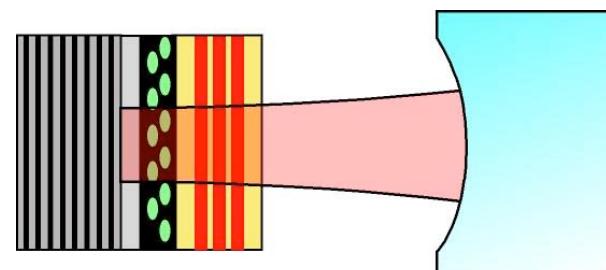
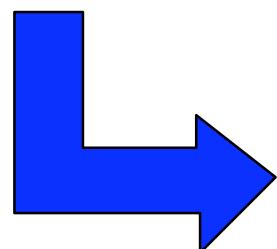
# Motivation for semiconductor lasers: Wafer scale integration

D. Lorensen et al., *Appl. Phys. B* **79**, 927, 2004



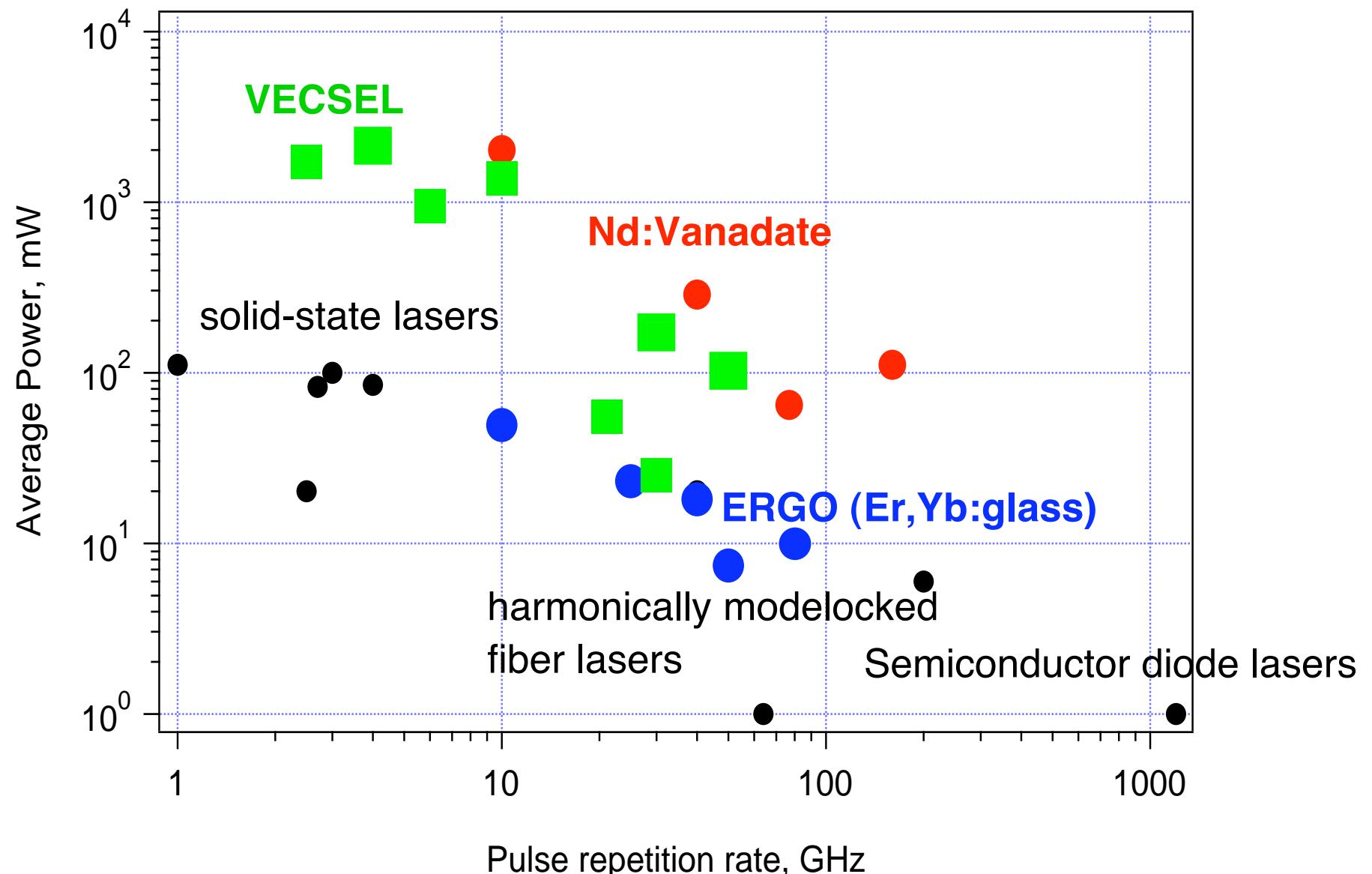
Passively modelocked VECSEL  
vertical **e**xternal **c**avity **s**urface **e**mitting **l**aser

Review: *Physics Reports* 429, 67-120, 2006

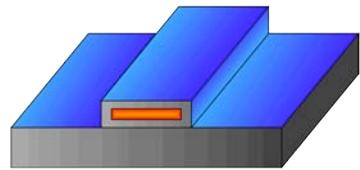


MIXSEL  
modellocked **i**ntegrated **e**xternal-cavity **s**urface **e**mitting **l**aser

# High pulse repetition rate sources

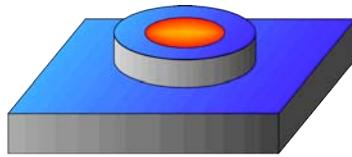


# How to Achieve High Powers



## Edge-emitting lasers

- Stripe width is limited by beam quality requirements for mode locking
- Nonlinearity and facet damage limit the peak powers



## Surface-emitting lasers

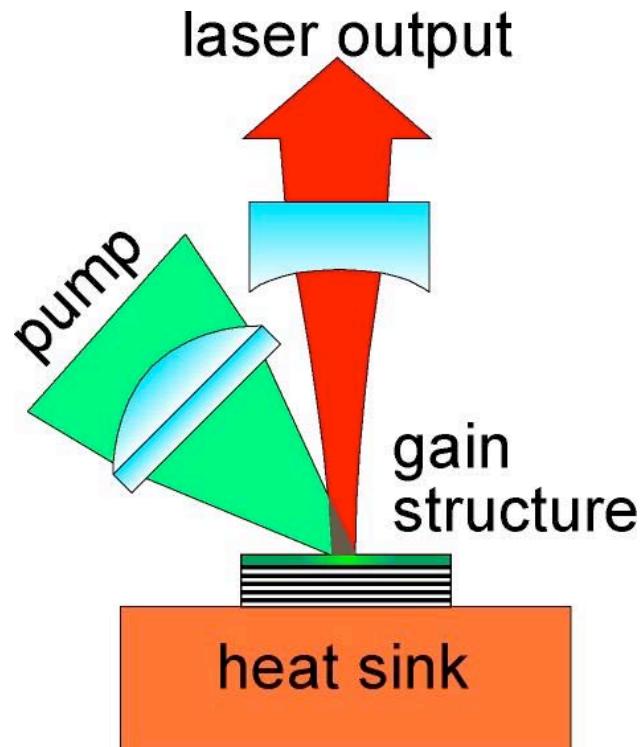
- Electrical pumping: ring electrode limits size
- Optical pumping: large area with homogeneous inversion
- External cavity needed (repetition rate 1 -100 GHz)

Optically pumped **Vertical-External-Cavity**  
**Surface-Emitting Laser (VECSEL)**

# CW optically pumped VECSEL

**OP-VECSEL** = Optically Pumped Vertical-External-Cavity Surface-Emitting Semiconductor Laser

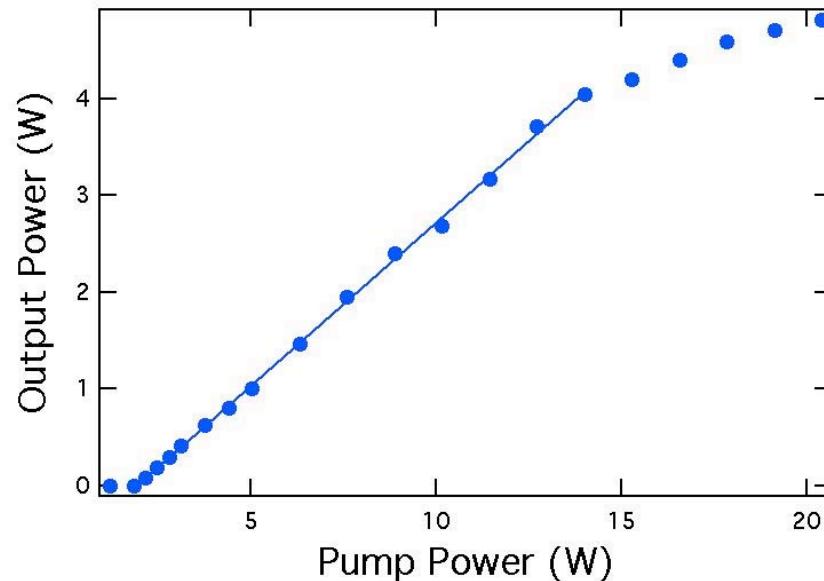
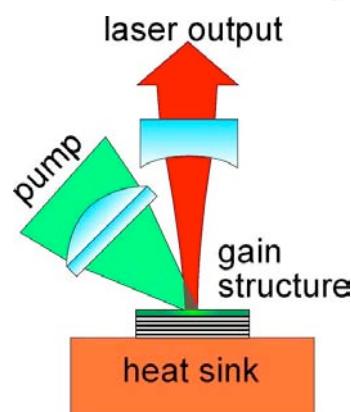
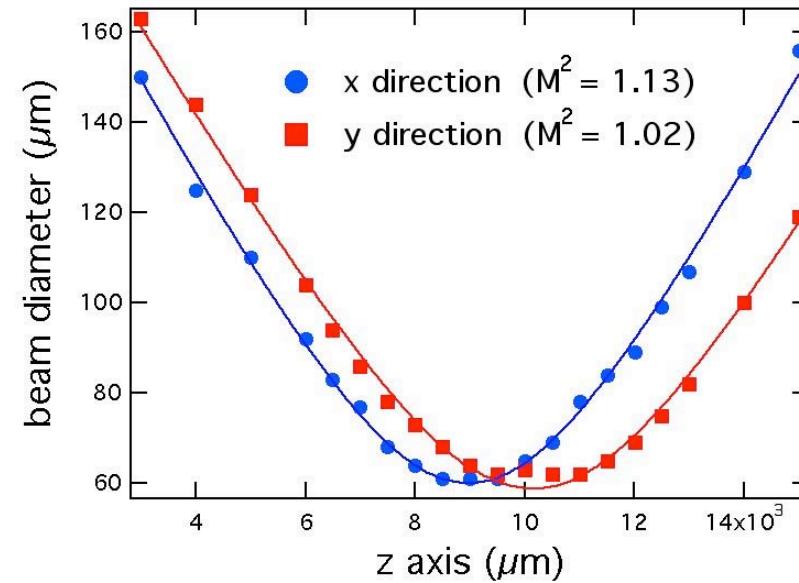
M. Kuznetsov et al., *IEEE Photon. Technol. Lett.* **9**, 1063 (1997)



- Semiconductor gain structure with reduced thickness
- Pump: high power diode bar
- External cavity for diffraction-limited output

## 4.4 W cw VECSEL (950 - 960 nm)

## Output vs. Input

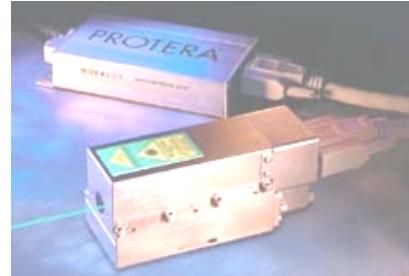
 $M^2$  measurement

- MOVPE, 7 InGaAs/GaAsP strain-compensated
- Output coupling 1.5%
- Heat sink temperature -5 °C
- 4.4 W out at 16.6 W pump power, 26% efficiency
- 34% slope efficiency
- $M^2 = (1.13, 1.02)$  in (x,y) direction

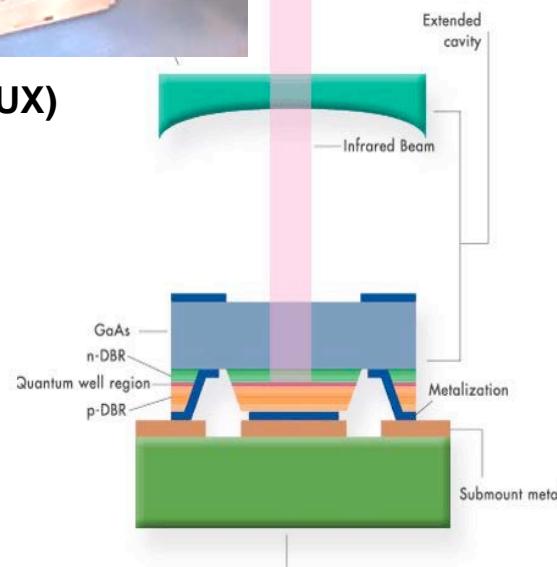
8-W VECSEL with  $M^2 < 1.8$  from Osram: S. Ludgen et al., APL 82 (21), 3620 (2003)

# Electrical or optical pumping ?

**Medium to high powers with good beam quality**

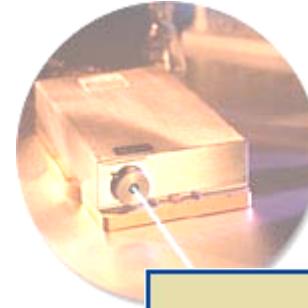


**(NOVALUX)**

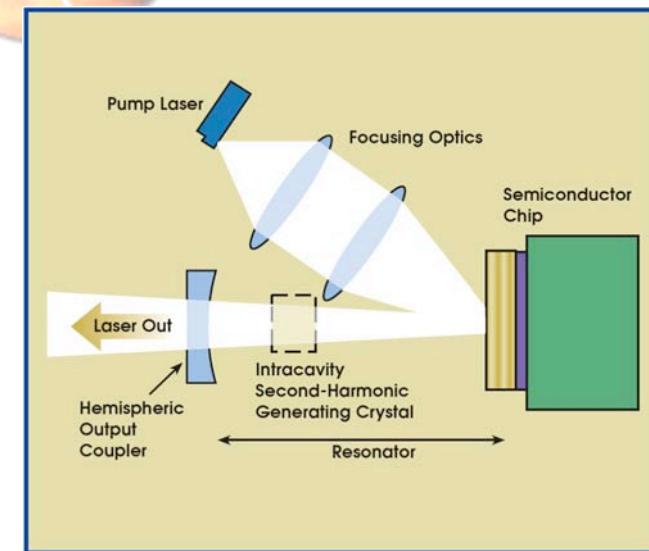


**Electrically pumped**

**Medium power:**  
up to 500 mW ( $\text{TEM}_{00}$ )



**(COHERENT)**



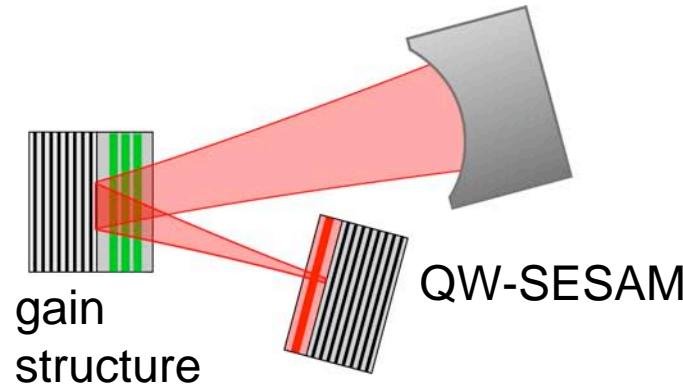
**Optically pumped**

**High power:**  
up to 30 W ( $M^2 = 3$ )

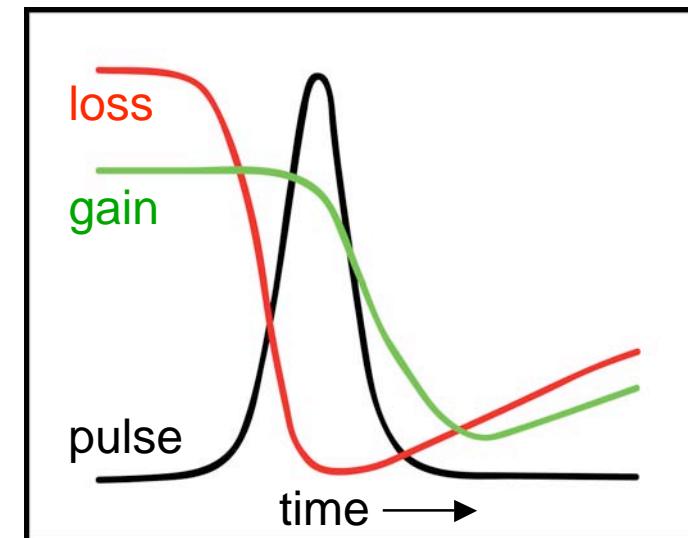
# OP-VECSEL milestones

- **First room temperature VECSEL:**  
**20 μW** average power: J.V. Sandusky et al., *IEEE Photon. Technol. Lett.* 8, 313 (1996)
  - **High-power cw operation:**  
**0.5 W** in TEM<sub>00</sub> beam: M. Kuznetsov et al., *IEEE Photon. Technol. Lett.* 9, 1063 (1997)  
**1.5 W**: W. J. Alford et al., *J. Opt. Soc. Am. B* 19, 663 (2002)  
**30 W**: J. Chilla et al., *Proc. SPIE* 5332, 143 (2004)
  - **Passive mode locking with SESAM:**  
**20 mW**: S. Hoogland et al., *IEEE Photon. Technol. Lett.* 12, 1135 (2000)  
**200 mW**: R. Häring et al., *Electron. Lett.* 37, 766 (2001)  
**950 mW**: R. Häring et al., *IEEE JQE* 38, 1268 (2002)  
**2.1 W**, 4.7 ps, 4 GHz, 957 nm: A. Aschwanden et al., *Opt. Lett.* 30, 272 (2005)
- Modelocked VECSEL review:** *Physics Reports* 429, 67, 2006

# VECSEL Modelocking



< 20 GHz



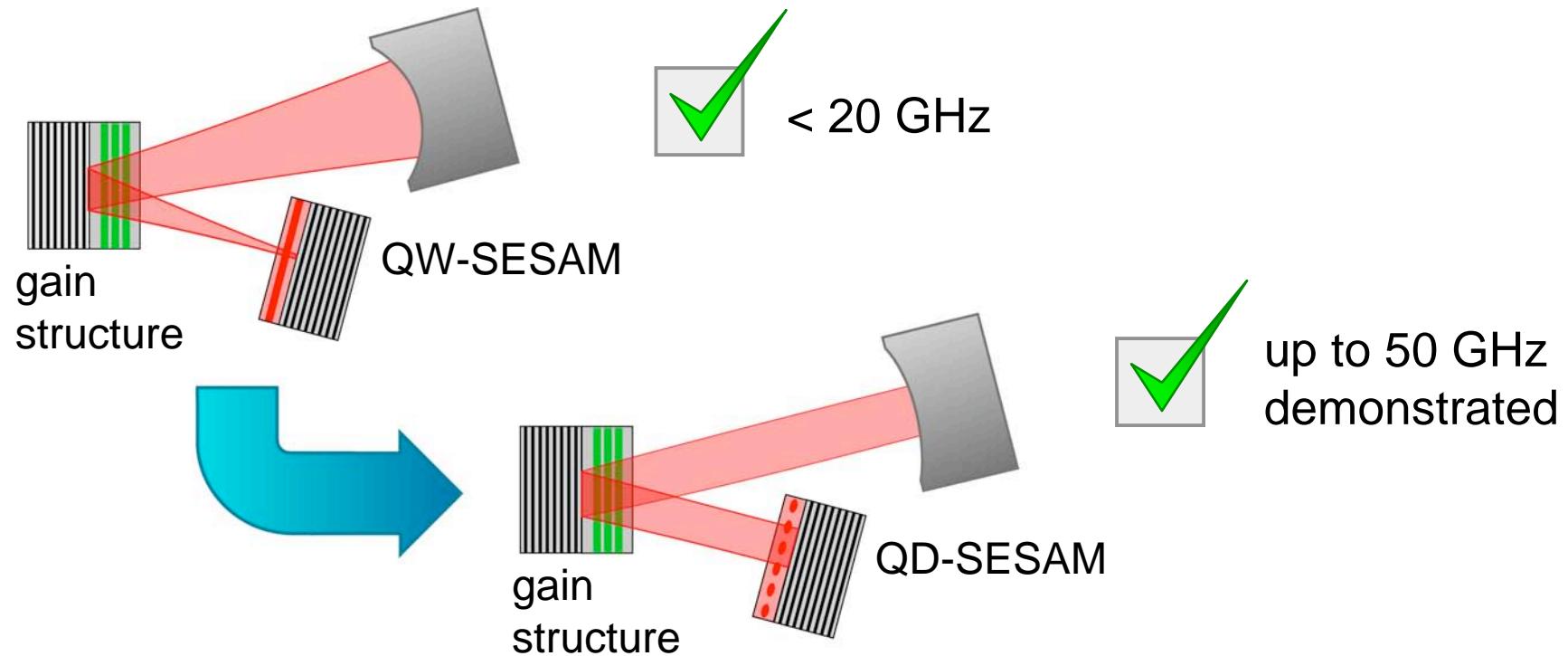
First passively mode-locked VECSEL:

S. Hoogland et al., IEEE Phot. Tech. Lett., vol. 12, pp. 1135-1138, 2000.

Highest output power (2.1 W):

A. Aschwanden et al., Opt. Lett., vol. 30, pp. 272-274, 2005.

# VECSEL Modelocking



First passively mode-locked VECSEL:

S. Hoogland et al., IEEE Phot. Tech. Lett., vol. 12, pp. 1135-1138, 2000.

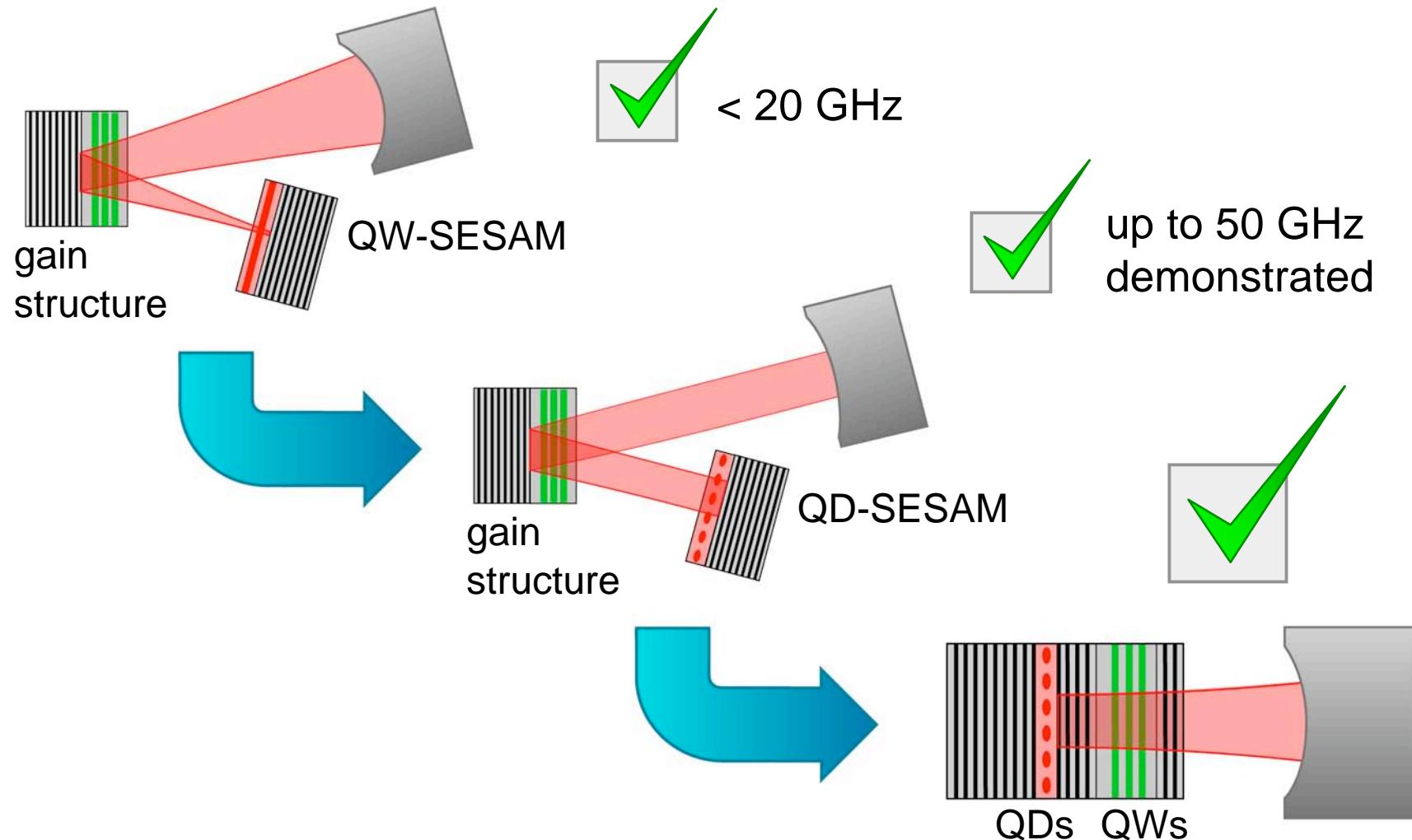
Highest output power (2.1 W):

A. Aschwanden et al., Opt. Lett., vol. 30, pp. 272-274, 2005.

QD-SESAM modelocking (50 GHz):

D. Lorensen et al., IEEE J. Quantum Electron., vol. 42, pp. 838-847, 2006.

# From VECSEL to MIXSEL



## MIXSEL

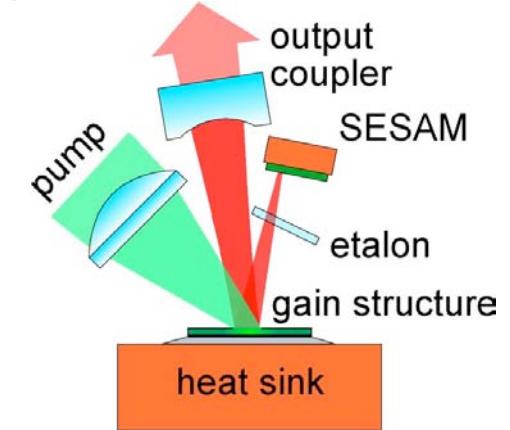
modelocked **i**ntegrated **e**xternal-cavity **s**urface **e**mitting **l**aser

## High-power ML VECSELs (up to **2.1 W** at **4 GHz**)

- High peak power (100 W) due to short pulses (few ps)

## ML VECSELs at $1.3 \mu\text{m}$ and $1.5 \mu\text{m}$

- InGaAsP-based: 3 GHz, 120 mW, 3.2 ps
- All GaInNAs-based: 6 GHz, 57 mW, 18.7 ps

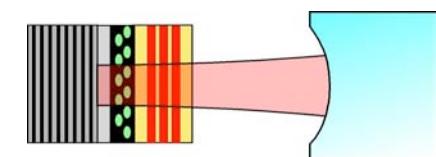


## High-repetition-rate ML VECSELs (up to **100 mW** at **50 GHz**)

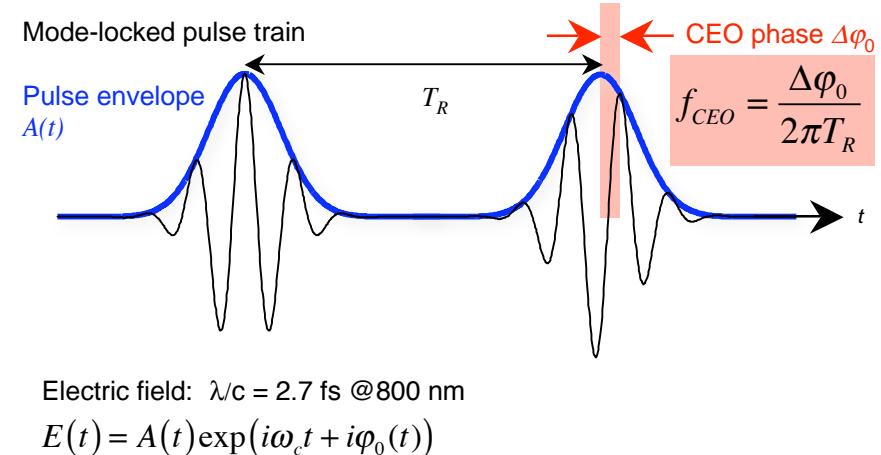
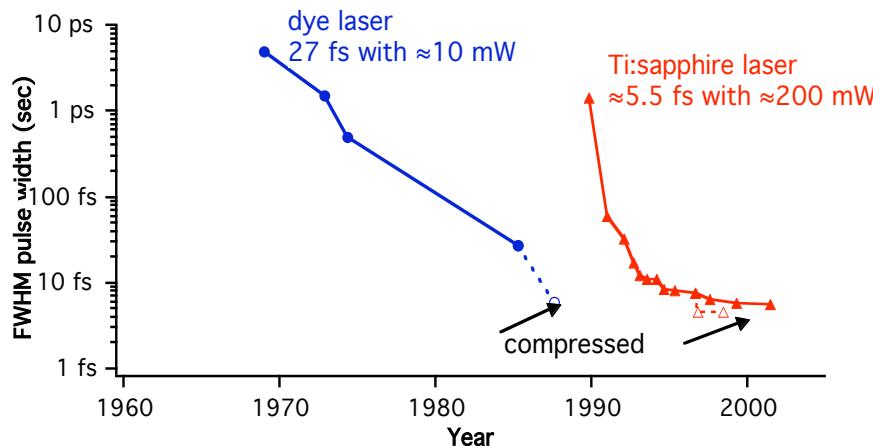
- Much higher average output power directly from oscillator than ML edge-emitting semiconductor lasers
- Demonstration of 1:1 mode locking proves the feasibility of integrating absorber and gain in same structure
- Applications: optical clocking of integrated circuits

## Future work

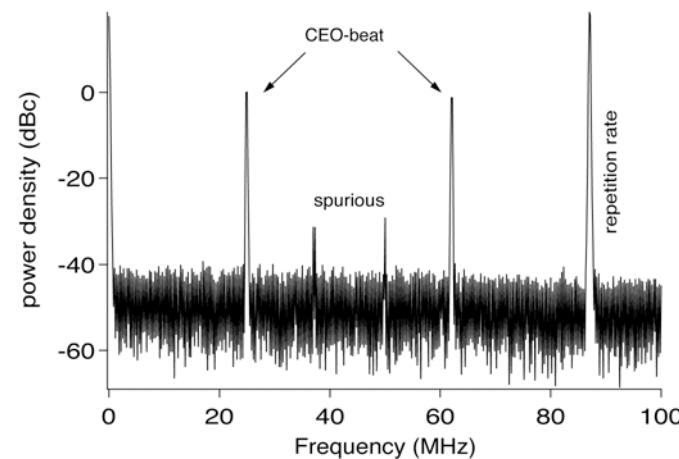
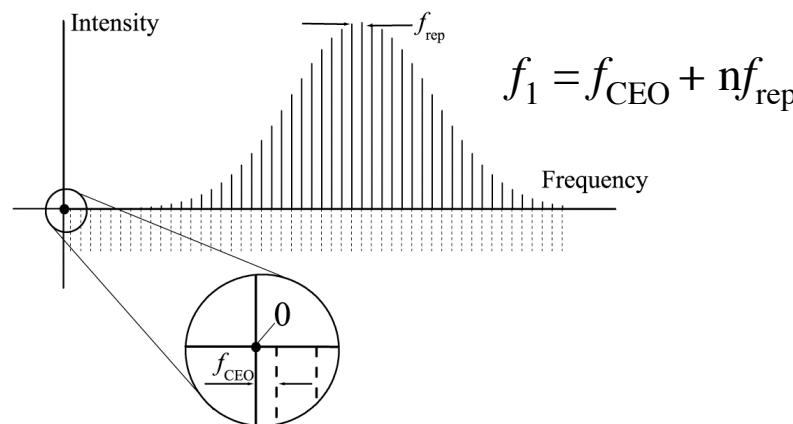
- Integration of absorber into gain structure
- Electrical pumping



# What is special about ultrafast solid-state lasers?



- **World record results in ultrashort pulse generation:** two-optical-cycle regime ( $\approx 5$  fs) using KLM and chirped mirrors, *Science* **286**, 1507, 1999
- **Carrier envelope offset (CEO) control and stabilization using frequency combs:** *Appl. Phys. B* **69**, 327, 1999 and *IEEE JSTQE* **9**, 1030, 2003



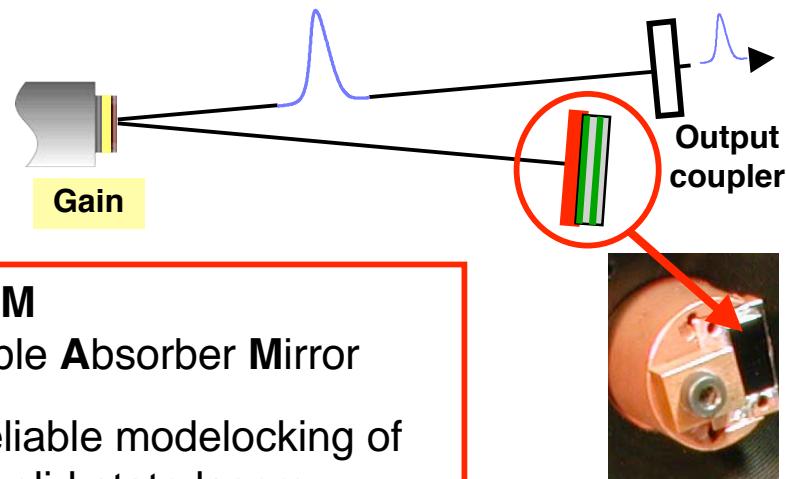
# What is special about ultrafast solid-state lasers?

U. Keller et al. *Opt. Lett.* **17**, 505, 1992

*IEEE JSTQE* **2**, 435, 1996

*Progress in Optics* **46**, 1-115, 2004

*Nature* **424**, 831, 2003

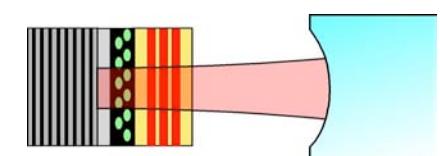


## SESAM

**SE**miciconductor **S**aturable **A**sorber **M**irror

self-starting, stable, and reliable modelocking of  
diode-pumped ultrafast solid-state lasers

- **Solved Q-switching problem** for passively modelocked diode-pumped solid-state lasers (after more than 25 years) - important for “real-world” applications
- **Pushed pulse energy** of diode-pumped ultrafast solid-state lasers by **four** orders of magnitude: Latest result **11 µJ**, 791 fs, 45 W, 4 MHz
- **Pushed pulse repetition rate** of diode-pumped solid-state lasers by more than two orders of magnitude: **160 GHz** at 1 µm and **77 GHz** at 1.5 µm
- **Passively modelocked vertical external-cavity surface-emitting laser (VECSEL):** for high pulse repetition rates, power scaling to 2.1 W, full wafer-scale integration  
Invited review paper in *Physics Reports* **429**, pp. 67-120, 2006
- **MIXSEL** - a new class of ultrafast semiconductor lasers



# Keller group: Thank you ...



## Ultrafast solid-state lasers: High average power (ML thin-disk laser)

Sergio Marchese, Cyrill Bär, Anna Enquist, Oliver Heckl, Dr. Thomas Südmeyer

## Ultrafast solid-state lasers: High pulse repetition rate

Max Stumpf, Andreas Oehler, Selina Pekarek, Dr. Thomas Südmeyer

## Ultrafast surface-emitting semiconductor lasers (ultrafast VECSELs and MIXSELs)

Deran Maas, Aude-Reine Bellancourt, Benjamin Rudin, Andreas Rutz, Martin Hoffmann, Dr. Yohan Barbarin, Dr. Thomas Südmeyer

## MBE and MOVPE growth in ETH clean room facility (FIRST-lab)

Dr. Matthias Golling

ETH FIRST Lab staff: Dr. Silke Schön (MBE), Dr. Emilio Gini (MOVPE)

## High field laser physics, attosecond pulse generation and science

Dr. Lukas Gallmann, Dr. Amelle Zair, Dr. Claudio Cirelli

Christian Erny, Petrissa Eckle, Mirko Holler, Florian Schlapper, Matthias Weger